



bq769x0 3-Series to 15-Series Cell Battery Monitor Family for Li-Ion and Phosphate Applications

1 Introduction

1.1 Features

- AFE Monitoring Features
 - Pure digital interface
 - Internal ADC measures cell voltage, die temperature, and external thermistor
 - A separate, internal ADC measures pack current (coulomb counter)
 - Directly supports up to three thermistors (103AT)
- Hardware Protection Features
 - Overcurrent in discharge (OCD)
 - Short circuit in discharge (SCD)
 - Overvoltage (OV)
- Undervoltage (UV)
- Secondary protector fault detection
- Additional Features
 - Integrated cell balancing FETs
 - Charge, discharge low-side NCH FET drivers
 - Alert interrupt to host microcontroller
 - 2.5-V or 3.3-V output voltage regulator
 - No EEPROM programming necessary
 - High supply voltage abs max (up to 108 V)
 - Simple I²C™ compatible interface (CRC option)
 - Random cell connection tolerant

1.2 Applications

- Light Electric Vehicles (LEV): eBikes, eScooters, Pedelec, and Pedal-Assist Bicycles
- Power and Gardening Tools
- Battery Backup and UPS Systems
- Wireless Base Station Backup Systems
- 12-V, 18-V, 24-V, 36-V, and 48-V Battery Packs

1.3 Description

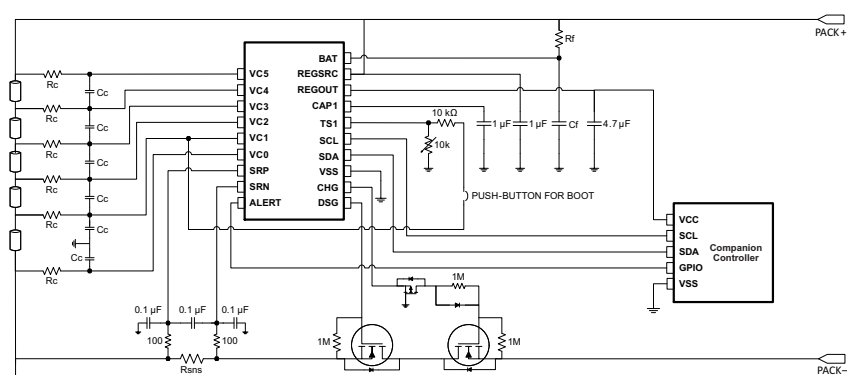
The bq769x0 family of robust analog front-end (AFE) devices serves as part of a complete pack monitoring and protection solution for next-generation, high-power systems, such as light electric vehicles, power tools, and uninterruptible power supplies. The bq769x0 is designed with low power in mind: Sub-blocks within the IC may be enabled/disabled to control the overall chip current consumption, and a SHIP mode provides a simple way to put the pack into an ultra-low power state.

Device Information⁽¹⁾

| PART NUMBER | PACKAGE | BODY SIZE (NOM) |
|-------------|------------|--------------------|
| bq76920 | TSSOP (20) | 6.50 mm × 4.40 mm |
| bq76930 | TSSOP (30) | 7.80 mm × 4.40 mm |
| bq76940 | TSSOP (44) | 11.00 mm × 4.40 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

1.4 Simplified System Diagram



Copyright © 2016, Texas Instruments Incorporated



Table of Contents

| | | | | | |
|----------|--|-----------|-----------|---|-----------|
| 1 | Introduction | 1 | 7 | Detailed Description | 20 |
| 1.1 | Features | 1 | 7.1 | Overview | 20 |
| 1.2 | Applications | 1 | 7.2 | Functional Block Diagram | 20 |
| 1.3 | Description | 1 | 7.3 | Feature Description | 21 |
| 1.4 | Simplified System Diagram | 1 | 7.4 | Device Functional Modes | 31 |
| 2 | Revision History | 2 | 7.5 | Register Maps | 33 |
| 3 | Description (Continued) | 4 | 8 | Application and Implementation | 43 |
| 4 | Device Comparison Table | 4 | 8.1 | Application Information | 43 |
| 5 | Pin Configuration and Functions | 5 | 8.2 | Typical Applications | 44 |
| 5.1 | Versions | 5 | 9 | Power Supply Recommendations | 50 |
| 5.2 | bq76920 Pin Diagram | 6 | 10 | Layout | 51 |
| 5.3 | bq76930 Pin Diagram | 7 | 10.1 | Layout Guidelines | 51 |
| 5.4 | bq76940 Pin Diagram | 9 | 10.2 | Layout Example | 51 |
| 6 | Specifications | 11 | 11 | Device and Documentation Support | 54 |
| 6.1 | Absolute Maximum Ratings | 11 | 11.1 | Documentation Support | 54 |
| 6.2 | ESD Ratings | 11 | 11.2 | Related Links | 54 |
| 6.3 | Recommended Operating Conditions | 11 | 11.3 | Trademarks | 54 |
| 6.4 | Thermal Information | 13 | 11.4 | Electrostatic Discharge Caution | 54 |
| 6.5 | Electrical Characteristics | 13 | 11.5 | Glossary | 54 |
| 6.6 | Timing Requirements | 18 | 12 | Mechanical, Packaging, and Orderable Information | 54 |
| 6.7 | Typical Characteristics | 19 | | | |

2 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

| Changes from Revision F (November 2015) to Revision G | Page |
|---|------|
| <ul style="list-style-type: none"> Changed <i>Electrical Characteristics</i> table to clarify the accuracy of the ADC in different temperature ranges..... | 14 |

| Changes from Revision E (November 2014) to Revision F | Page |
|--|--|
| <ul style="list-style-type: none"> Changed bq7693002 From: Product Preview To Production in the <i>Device Comparison Table</i>..... Added bq7693007 device to the <i>Device Comparison Table</i> Changed table note to group ground reference in <i>bq76930 Pin Functions</i> Changed table note to group ground reference in <i>bq76940 Pin Functions</i> Changed 10th cell to 11th cell in the Description of pin 29 Changed table formats for online data sheet Changed <i>Handling Ratings</i> table to <i>ESD Ratings</i> Changed note for R1 on Figure 7-3..... Added more description to the <i>Communications Subsystem</i> section Changed "SHUTA" to "SHUT_A" and "SHUTB" to "SHUT_B" in the <i>SHIP Mode</i> section Changed CAUTION verbiage (editorial)..... Changed the SHUT_A, SHUT_B bit descriptions in the <i>SYS_CTRL1 (0x04)</i> table | 4 4 7 9 10 11 11 27 30 32 32 36 |

| Changes from Revision D (July 2014) to Revision E | Page |
|--|--|
| <ul style="list-style-type: none"> Added a note to the <i>Absolute Maximum Ratings</i> table Changed the <i>Handling Ratings</i>..... Added the cross-reference to a new table note at V_{ALERT_IH} in <i>Electrical Characteristics</i> Added a new table note Added the <i>Typical Characteristics</i> section Changed the <i>Alert</i> section Changed verbiage in <i>Communications Subsystem</i> | 11 11 17 17 19 29 30 |

| | |
|---|--------------------|
| • Deleted the READ/WRITE RSVD register in the <i>Register Map</i> | 33 |
| • Deleted the READ ONLY register information in the <i>Register Map</i> | 33 |
| • Changed the reset for Bit 3 in the PROTECT3 register | 38 |
| • Changed wording in the ADCGAIN bit descriptions | 41 |
| • Added <i>Application and Implementation</i> note | 43 |
| • Added <i>Design Requirements</i> | 46 |
| • Added the <i>Detailed Design Procedure</i> | 47 |
| • Changed the <i>Layout Guidelines</i> | 51 |
| • Changed the <i>Layout Example</i> | 51 |
| • Added a <i>Caution</i> | 51 |
| • Changed the Good Layout figure | 52 |
| • Changed the Weak Layout figure | 53 |

| Changes from Revision C (May 2014) to Revision D | Page |
|--|--------------------|
| • Changed table reference in <i>Integrated Hardware Protections</i> | 26 |
| • Changed paragraph 4 verbiage of <i>Integrated Hardware Protections</i> | 26 |

| Changes from Revision B (April 2014) to Revision C | Page |
|--|--------------------|
| • Changed the documentation format | 1 |
| • Changed some devices from Product Preview to Production Data | 4 |
| • Changed a bit name in the PROTECT1 register | 37 |
| • Changed a bit name in the ADCGAIN2 register | 42 |

| Changes from Revision A (December 2013) to Revision B | Page |
|---|--------------------|
| • Changed title of the data manual | 1 |
| • Changed Ordering Information table to | 4 |
| • Changed some devices to Product Preview | 4 |
| • Changed R _I max value in the <i>Recommended Operating Conditions</i> table | 12 |
| • Changed verbiage in <i>mmunications Subsystem</i> | 30 |
| • Changed SYS_STAT D6 bit name in the <i>Register Map</i> | 33 |

| Changes from Original (October 2013) to Revision A | Page |
|--|--------------------|
| • Changed some devices from Product Preview to Production Data | 4 |
| • Changed the t _{INDCELL} test condition in <i>Electrical Characteristics</i> | 14 |
| • Deleted duplicate CELLBAL3 table | 35 |
| • Changed bq76940 with bq783xx Companion Controller IC Schematic | 46 |

3 Description (Continued)

The bq76920 device supports up to 5-series cells or typical 18-V packs, the bq76930 handles up to 10-series cells or typical 36-V packs, and the bq76940 works for up to 15-series cells or typical 48-V packs. A variety of battery chemistries may be managed with these AFEs, including Lithium Ion, Lithium iron phosphate, and more.

Via I²C, a host controller can use the bq769x0 to implement many battery pack management functions, such as monitoring (cell voltages, pack current, pack temperatures), protection (controlling charge/discharge FETs), and balancing. Integrated A/D converters enable a purely digital readout of critical system parameters, with calibration handled in TI's manufacturing process.

4 Device Comparison Table

| TUBE | TAPE & REEL | CELLS | I ² C ADDRESS (7-Bit) | LDO (V) | CRC | PACKAGE | |
|----------------------------|-----------------------------|-------|----------------------------------|---------|-----|----------------|--|
| bq7692000PW | bq7692000PWR | 3–5 | 0x08 | 2.5 | No | 20-TSSOP (PW) | |
| bq7692001PW ⁽¹⁾ | bq7692001PWR ⁽¹⁾ | | | | Yes | | |
| bq7692002PW ⁽¹⁾ | bq7692002PWR ⁽¹⁾ | | | 3.3 | No | | |
| bq7692003PW | bq7692003PWR | | Yes | | | | |
| bq7692006PW | bq7692006PWR | | 0x18 | | No | | |
| bq7693000DBT | bq7693000DBTR | 6–10 | 0x08 | 2.5 | No | 30-TSSOP (DBT) | |
| bq7693001DBT | bq7693001DBTR | | | | Yes | | |
| bq7693002DBT | bq7693002DBTR | | | 3.3 | No | | |
| bq7693003DBT | bq7693003DBTR | | Yes | | | | |
| bq7693006DBT | bq7693006DBTR | | 0x18 | | No | | |
| bq7693007DBT | bq7693007DBTR | | 0x18 | | Yes | | |
| bq7694000DBT | bq7694000DBTR | 9–15 | 0x08 | 2.5 | No | 44-TSSOP (DBT) | |
| bq7694001DBT | bq7694001DBTR | | | | Yes | | |
| bq7694002DBT | bq7694002DBTR | | | 3.3 | No | | |
| bq7694003DBT | bq7694003DBTR | | Yes | | | | |
| bq7694006DBT | bq7694006DBTR | | 0x18 | | No | | |

(1) Product Preview only

Texas Instruments pre-configures the bq769x0 devices for a specific I²C address, LDO voltage, and more. These settings are permanently stored in EEPROM and cannot be further modified.

Contact Texas Instruments for other options not listed above, as well as any options noted as “Product Preview only.”

5 Pin Configuration and Functions

5.1 Versions

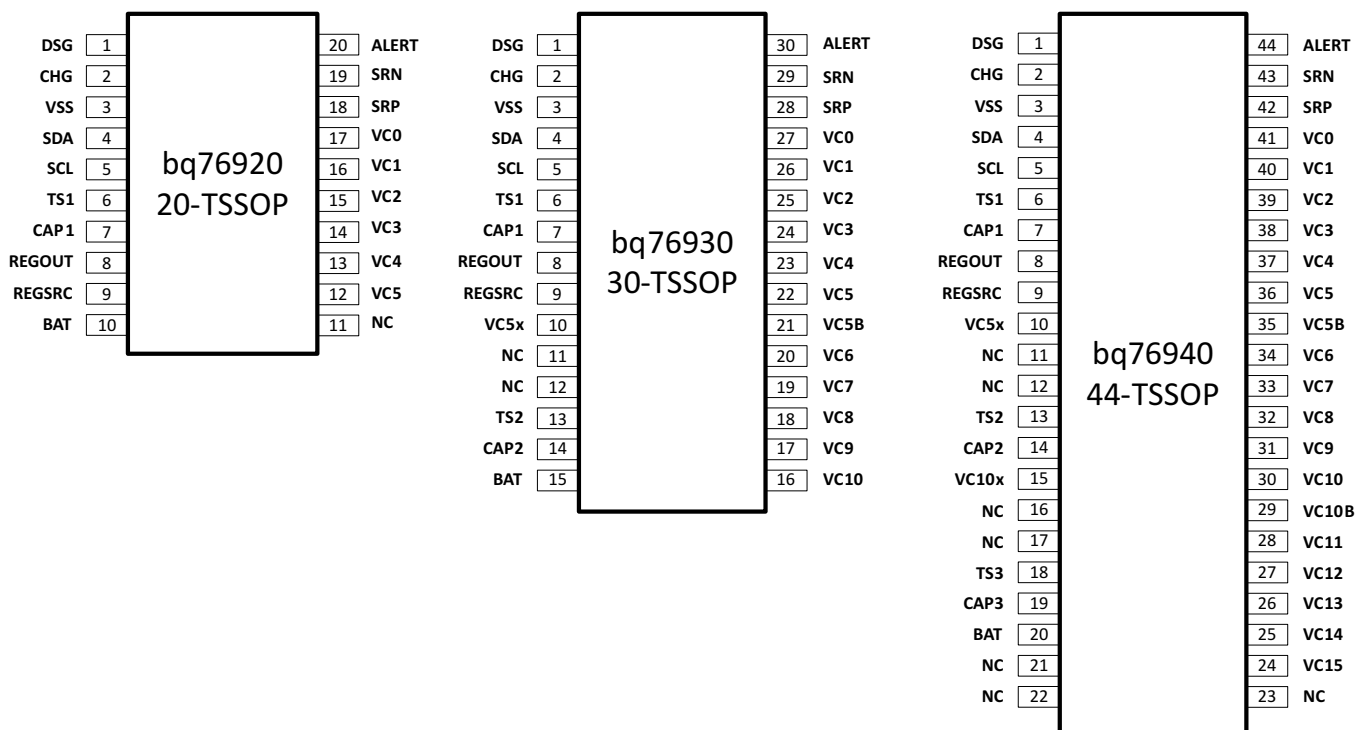


Figure 5-1. Pin Versions

bq76920: 3–5 Series Cells (20-TSSOP)

- 6.5 mm x 4.4 mm x 1.2 mm

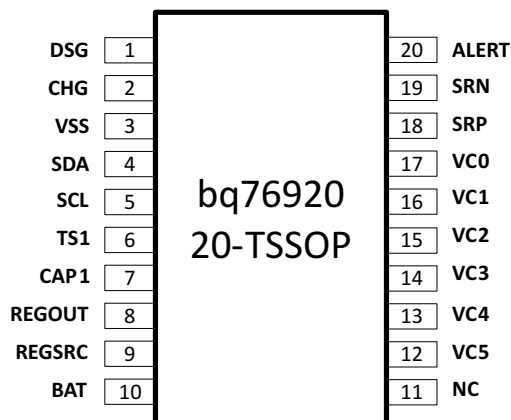
bq76930: 6–10 Series Cells (30-TSSOP)

- 7.8 mm x 4.4 mm x 1.2 mm

bq76940: 9–15 Series Cells (44-TSSOP)

- 11.3 mm x 4.4 mm x 1.2 mm

5.2 bq76920 Pin Diagram



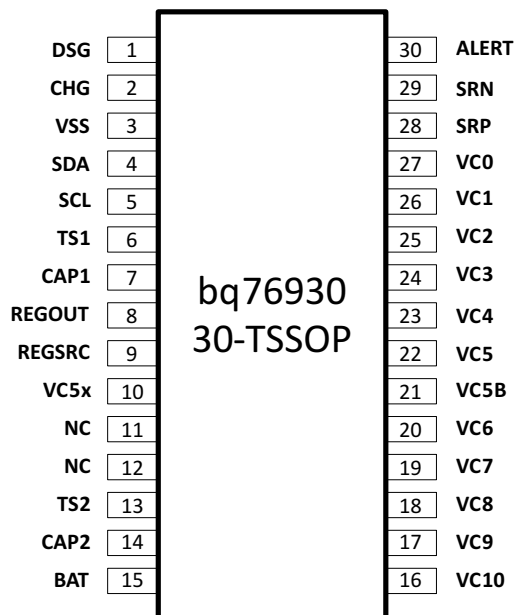
5.2.1 bq76920 Pin Map

bq76920 Pin Functions

| PIN | NAME | TYPE | DESCRIPTION |
|-----|--------|------|---|
| 1 | DSG | O | Discharge FET driver |
| 2 | CHG | O | Charge FET driver |
| 3 | VSS | — | Chip VSS |
| 4 | SDA | I/O | I ² C communication to the host controller |
| 5 | SCL | I | I ² C communication to the host controller |
| 6 | TS1 | I | Thermistor #1 positive terminal ⁽¹⁾ |
| 7 | CAP1 | O | Capacitor to VSS |
| 8 | REGOUT | P | Output LDO |
| 9 | REGSRC | I | Input source for output LDO |
| 10 | BAT | P | Battery (top-most) terminal |
| 11 | NC | — | No connect |
| 12 | VC5 | I | Sense voltage for 5th cell positive terminal |
| 13 | VC4 | I | Sense voltage for 4th cell positive terminal |
| 14 | VC3 | I | Sense voltage for 3rd cell positive terminal |
| 15 | VC2 | I | Sense voltage for 2nd cell positive terminal |
| 16 | VC1 | I | Sense voltage for 1st cell positive terminal |
| 17 | VC0 | I | Sense voltage for 1st cell negative terminal |
| 18 | SRP | I | Negative current sense (nearest VSS) |
| 19 | SRN | I | Positive current sense |
| 20 | ALERT | I/O | Alert output and override input |

(1) If not used, pull down to VSS with a 10-kΩ nominal resistor.

5.3 bq76930 Pin Diagram



5.3.1 bq76930 Pin Map

bq76930 Pin Functions

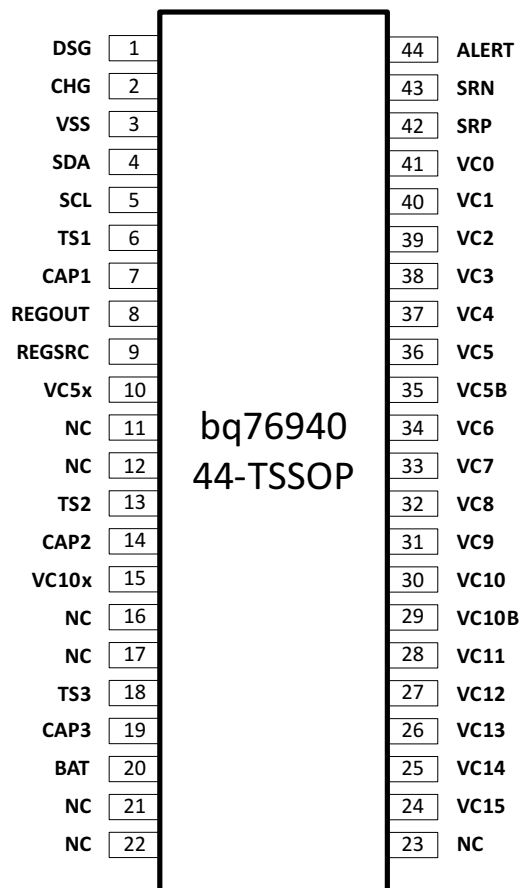
| PIN | NAME | TYPE | DESCRIPTION |
|-----|--------|------|---|
| 1 | DSG | O | Discharge FET driver |
| 2 | CHG | O | Charge FET driver |
| 3 | VSS | — | Chip VSS |
| 4 | SDA | I/O | I ² C communication to the host controller |
| 5 | SCL | I | I ² C communication to the host controller |
| 6 | TS1 | I | Thermistor #1 positive terminal ⁽¹⁾ |
| 7 | CAP1 | O | Capacitor to VSS |
| 8 | REGOUT | P | Output LDO |
| 9 | REGSRC | I | Input source for output LDO |
| 10 | VC5X | P | Thermistor #2 negative terminal |
| 11 | NC | — | No connect (short to CAP2) |
| 12 | NC | — | No connect (short to CAP2) |
| 13 | TS2 | I | Thermistor #2 positive terminal ⁽¹⁾ |
| 14 | CAP2 | O | Capacitor to VC5X |
| 15 | BAT | P | Battery (top-most) terminal |
| 16 | VC10 | I | Sense voltage for 10th cell positive terminal |
| 17 | VC9 | I | Sense voltage for 9th cell positive terminal |
| 18 | VC8 | I | Sense voltage for 8th cell positive terminal |
| 19 | VC7 | I | Sense voltage for 7th cell positive terminal |
| 20 | VC6 | I | Sense voltage for 6th cell positive terminal |
| 21 | VC5B | I | Sense voltage for 6th cell negative terminal |
| 22 | VC5 | I | Sense voltage for 5th cell positive terminal |
| 23 | VC4 | I | Sense voltage for 4th cell positive terminal |

(1) If not used, pull down to group ground reference (VSS for TS1 and VC5X for TS2) with a 10-kΩ nominal resistor.

bq76930 Pin Functions (continued)

| PIN | NAME | TYPE | DESCRIPTION |
|-----|-------|------|--|
| 24 | VC3 | I | Sense voltage for 3rd cell positive terminal |
| 25 | VC2 | I | Sense voltage for 2nd cell positive terminal |
| 26 | VC1 | I | Sense voltage for 1st cell positive terminal |
| 27 | VC0 | I | Sense voltage for 1st cell negative terminal |
| 28 | SRP | I | Negative current sense (nearest VSS) |
| 29 | SRN | I | Positive current sense |
| 30 | ALERT | I/O | Alert output and override input |

5.4 bq76940 Pin Diagram



5.4.1 bq76940 Pin Map

bq76940 Pin Functions

| PIN | NAME | TYPE | DESCRIPTION |
|-----|--------|------|---|
| 1 | DSG | O | Discharge FET driver |
| 2 | CHG | O | Charge FET driver |
| 3 | VSS | — | Chip VSS |
| 4 | SDA | I/O | I ² C communication to the host controller |
| 5 | SCL | I | I ² C communication to the host controller |
| 6 | TS1 | I | Thermistor #1 positive terminal ⁽¹⁾ |
| 7 | CAP1 | O | Capacitor to VSS |
| 8 | REGOUT | P | Output LDO |
| 9 | REGSRC | I | Input source for output LDO |
| 10 | VC5X | P | Thermistor #2 negative terminal |
| 11 | NC | — | No connect (short to CAP2) |
| 12 | NC | — | No connect (short to CAP2) |
| 13 | TS2 | I | Thermistor #2 positive terminal ⁽¹⁾ |
| 14 | CAP2 | O | Capacitor to VC5X |
| 15 | VC10X | P | Thermistor #3 negative terminal |

(1) If not used, pull down to group ground reference (VSS for TS1, VC5X for TS2, and VC10X for TS3) with a 10-kΩ nominal resistor.

bq76940 Pin Functions (continued)

| PIN | NAME | TYPE | DESCRIPTION |
|-----|-------|------|--|
| 16 | NC | — | No connect (short to CAP3) |
| 17 | NC | — | No connect (short to CAP3) |
| 18 | TS3 | I | Thermistor #3 positive terminal ⁽¹⁾ |
| 19 | CAP3 | O | Capacitor to VC10X |
| 20 | BAT | P | Battery (top-most) terminal |
| 21 | NC | — | No connect |
| 22 | NC | — | No connect |
| 23 | NC | — | No connect |
| 24 | VC15 | I | Sense voltage for 15th cell positive terminal |
| 25 | VC14 | I | Sense voltage for 14th cell positive terminal |
| 26 | VC13 | I | Sense voltage for 13th cell positive terminal |
| 27 | VC12 | I | Sense voltage for 12th cell positive terminal |
| 28 | VC11 | I | Sense voltage for 11th cell positive terminal |
| 29 | VC10B | I | Sense voltage for 11th cell negative terminal |
| 30 | VC10 | I | Sense voltage for 10th cell positive terminal |
| 31 | VC9 | I | Sense voltage for 9th cell positive terminal |
| 32 | VC8 | I | Sense voltage for 8th cell positive terminal |
| 33 | VC7 | I | Sense voltage for 7th cell positive terminal |
| 34 | VC6 | I | Sense voltage for 6th cell positive terminal |
| 35 | VC5B | I | Sense voltage for 6th cell negative terminal |
| 36 | VC5 | I | Sense voltage for 5th cell positive terminal |
| 37 | VC4 | I | Sense voltage for 4th cell positive terminal |
| 38 | VC3 | I | Sense voltage for 3rd cell positive terminal |
| 39 | VC2 | I | Sense voltage for 2nd cell positive terminal |
| 40 | VC1 | I | Sense voltage for 1st cell positive terminal |
| 41 | VC0 | I | Sense voltage for 1st cell negative terminal |
| 42 | SRP | I | Negative current sense (nearest VSS) |
| 43 | SRN | I | Positive current sense |
| 44 | ALERT | I/O | Alert output and override input |

6 Specifications

6.1 Absolute Maximum Ratings

Over-operating free-air temperature range (unless otherwise noted)

| | | | MIN | MAX | UNIT |
|------------------|--|---|------|-----------------------|------|
| V _{BAT} | Supply voltage | (BAT–VSS) | –0.3 | 36 | V |
| | | (BAT–VC5x), (VC5x–VSS) | | | |
| | | (BAT–VC10x), (VC10x–VC5x), (VC5x–VSS) | | | |
| V _I | Input voltage | (VCn–VSS) where n = 1..5 | –0.3 | (n × 7.2) | V |
| | | (VCn–VSS) where n = 1..5, (VCn–VC5x) where n = 6..10 | | | |
| | | (VCn–VSS) where n = 1..5, (VCn–VC5x) where n = 6..10, (VCn–VC10x) where n = 11..15 | | | |
| | | Cell input pins, differential (VCn–VCn–1) where n = 1..15/10/5 (bq76940/bq76930/bq76920, respectively) | –0.3 | 9 | V |
| | | SRN, SRP, SCL, SDA | –0.3 | 3.6 | V |
| | | (VC0–VSS), (CAP1–VSS), (TS1–VSS) ⁽¹⁾ | | | |
| | | (VC0–VSS), (VC5b–VC5x), (CAP2–VC5x), (CAP1–VSS), (TS2–VC5x), (TS1–VSS) ⁽¹⁾ | | | |
| V _O | Output voltage | (VC0–VSS), (VC5b–VC5x), (VC10b–VC10x), (CAP3–VC10x), (CAP2–VC5x), (CAP1–VSS), (TS3–VC10x), (TS2–VC5x), (TS1–VSS) ⁽¹⁾ | –0.3 | 36 | V |
| | | REGSRC | | | |
| | | REGOUT, ALERT | –0.3 | 3.6 | |
| | | DSG | –0.3 | 20 | V |
| I _{CB} | Cell balancing current (per cell) | CHG | –0.3 | V _{CHGCLAMP} | |
| | | bq76920 | 70 | | mA |
| I _{DSG} | Discharge pin input current when disabled (measured into terminal) | bq76930, bq76940 | 5 | | mA |
| | | | 7 | | mA |
| T _{STG} | Storage temperature | | –65 | 150 | °C |
| | Lead temperature (soldering, 10 s) | | | 300 | |

(1) The Absolute Maximum Ratings for (TS1–VSS) apply after the device completes POR and should be observed after t_{BOOTREADY} (10 ms), following the application of the boot signal on TS1. Prior to completion of POR, TS1 should not exceed 5 V.

6.2 ESD Ratings

| | | | VALUE | UNIT |
|--------------------|-------------------------|--|-------|------|
| V _(ESD) | Electrostatic discharge | Human body model (HBM) ESD stress voltage ⁽¹⁾ | ±2 | kV |
| | | Charged device model (CDM) ESD stress voltage ⁽²⁾ | ±500 | V |

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

Over-operating free-air temperature range (unless otherwise noted). See [Section 8.1.1](#) for more information on cell configurations. All voltages are relative to VSS, except "Cell input differential."

| | | | MIN | TYP | MAX | UNIT |
|------------------|----------------|---------------------------------------|-----|-----|-----|------|
| V _{BAT} | Supply voltage | (BAT–VSS) | 6 | | 25 | V |
| | | (BAT–VC5x), (VC5x–VSS) | | | | |
| | | (BAT–VC10x), (VC10x–VC5x), (VC5x–VSS) | | | | |

Recommended Operating Conditions (continued)

Over-operating free-air temperature range (unless otherwise noted). See [Section 8.1.1](#) for more information on cell configurations. All voltages are relative to VSS, except "Cell input differential."

| | | | MIN | TYP | MAX | UNIT | |
|--------------------|--|---|---------|------|-------|------|-----|
| V _{IN} | Input voltage | Cell input pins, differential (VC _n –VC _{n–1}) where n = 1..15/10/5 (bq76940/bq76930/bq76920, respectively), in-use cells only | 2 | | 5 | V | |
| | | (VC _n –VSS) where n = 1..5 | bq76920 | 0 | 5 × n | V | |
| | | (VC _n –VSS) where n = 1..5, (VC _n –VC5x) where n = 6..10 | bq76930 | | | | |
| | | (VC _n –VSS) where n = 1..5, (VC _n –VC5x) where n = 6..10, (VC _n –VC10x) where n = 11..15 | bq76940 | | | | |
| | | SRP | | | | | –10 |
| | | (VC0–VSS) | bq76920 | | | | |
| | | (VC0–VSS), (VC5b–VC5x) | bq76930 | | | | |
| | | (VC0–VSS), (VC5b–VC5x), (VC10b–VC10x) | bq76940 | | | | |
| | | SRN | | –200 | 200 | mV | |
| | | SCL, SDA | | 0 | 3.6 | V | |
| | | (TS1–VSS) | bq76920 | | | | |
| | | (TS1–VSS), (TS2–VC5x) | bq76930 | | | | |
| | | (TS1–VSS), (TS2–VC5x), (TS3–VC10x) | bq76940 | | | | |
| | | REGSRC | | 6 | 25 | | |
| V _{OUT} | Output voltage | CHG, DSG | 0 | 16 | V | | |
| | | REGOUT, ALERT | | 0 | 3.6 | V | |
| | | (CAP1–VSS) | bq76920 | | | | |
| | | (CAP1–VSS), (CAP2–VC5x) | bq76930 | | | | |
| | | (CAP1–VSS), (CAP2–VC5x), (CAP3–VC10x) | bq76940 | | | | |
| I _{CB} | Cell balancing current (internal, per cell) | bq76920 | | 0 | 50 | mA | |
| | | bq76930, bq76940 | | 0 | 5 | mA | |
| R _C | External cell input resistance | bq76920 | | 40 | 100 | 1K | Ω |
| | | bq76930, bq76940 | | 500 | 1K | 1K | Ω |
| C _C | External cell input capacitance | | 0.1 | 1 | 10 | μF | |
| R _f | External supply filter resistance | | 40 | 100 | 1K | Ω | |
| C _f | External supply filter capacitance | | 1 | 10 | 40 | μF | |
| R _{FILT} | Sense resistor filter resistance | | 100 | 1K | | Ω | |
| R _{ALERT} | ALERT pin to VSS resistor | | | 1M | | Ω | |
| C _L | REGOUT loading capacitance | | 1 | 4.7 | | μF | |
| C _{CAP} | REGSRC, CAP1, CAP2, and CAP3 output capacitance | | 1 | | | μF | |
| R _{TS} | External thermistor nominal resistance (103AT) at 25°C | | 10K | | | Ω | |
| T _{OPR} | Operating free-air temperature | | –40 | | 85 | °C | |

6.4 Thermal Information

Over-operating free-air temperature range (unless otherwise noted)

| THERMAL METRIC ⁽¹⁾ | TSSOP | | | UNIT |
|---|---------------------------|----------------------------|----------------------------|------|
| | bq76920xy 20 PINS (PW) | bq76930xy 30 PINS (DBT) | bq76940xy 44 PINS (DBT) | |
| R _{θJA, High K} Junction-to-ambient thermal resistance ⁽²⁾ | 93.7 | 86.5 | 70.1 | °C/W |
| R _{θJC(top)} Junction-to-case(top) thermal resistance ⁽³⁾ | 28.7 | 19.4 | 17.5 | °C/W |
| R _{θJB} Junction-to-board thermal resistance ⁽⁴⁾ | 44.6 | 41.3 | 33.9 | °C/W |
| Ψ _{JT} Junction-to-top characterization parameter ⁽⁵⁾ | 1.3 | 0.5 | 0.5 | °C/W |
| Ψ _{JB} Junction-to-board characterization parameter ⁽⁶⁾ | 44.1 | 40.6 | 33.4 | °C/W |
| R _{θJC(bottom)} Junction-to-case(bottom) thermal resistance ⁽⁷⁾ | n/a | n/a | n/a | °C/W |

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report ([SPRA953](#)).
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, Ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining R_{θJA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, Ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining R_{θJA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

6.5 Electrical Characteristics

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with V_{CELL} = 4 V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

| PARAMETER | | TEST CONDITION | MIN | TYP | MAX | UNIT |
|------------------------|------------------------------|---|-----|-----|-----|------|
| SUPPLY CURRENTS | | | | | | |
| I _{DD} | NORMAL mode: ADC off, CC off | Sum of ICC_BAT and ICC_REGSRC currents | | 40 | 60 | μA |
| | NORMAL mode: ADC on, CC off | | | 60 | 90 | |
| | NORMAL mode: ADC off, CC on | | | 110 | 165 | |
| | NORMAL mode: ADC on, CC on | | | 130 | 195 | |
| I _{CC_BAT} | NORMAL mode: ADC off | Into BAT pin | | 30 | 45 | |
| | NORMAL mode: ADC on | | | 50 | 75 | |
| I _{CC_REGSRC} | NORMAL mode: CC off | Into REGSRC pin | | 10 | 15 | |
| | NORMAL mode: CC on | | | 80 | 120 | |
| I _{SHIP} | SHIP/SHUTDOWN mode | Device in full shutdown, only VSTUP/BG and BOOT detector on | | 0.6 | 1.8 | |

Electrical Characteristics *(continued)*

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with $V_{CELL} = 4$ V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

| PARAMETER | | TEST CONDITION | MIN | TYP | MAX | UNIT |
|--|--|--|------|------|-----|------|
| LEAKAGE AND OFFSET CURRENTS | | | | | | |
| dI_{NOM} | NORMAL mode supply current offset | Measured into VC5x (bq76930, bq76940) and VC10x (bq76940) | –5 | ±2.5 | 5 | µA |
| dI_{SHIP} | SHIP mode supply current offset | | –1.0 | ±0.1 | 1.0 | |
| dI_{ALERT} | Supply current when ALERT active | Measured into VC5x (bq76930, bq76940) or added to BAT (bq76920) | | 15 | 25 | |
| dI_{CELL} | Cell measurement input current | Measured into VC0–VC15 except VC5, VC10, VC15 | –0.3 | ±0.1 | 0.3 | |
| | | Measured into VC5, VC10, VC15 | | | 0.5 | |
| I_{LKG} | Terminal input leakage | | | | 1 | |
| INTERNAL POWER CONTROL (STARTUP and SHUTDOWN) | | | | | | |
| V_{PORA} | Analog POR threshold | See Note ⁽¹⁾ | 4 | | 5 | V |
| V_{SHUT} | Shutdown voltage | See Note ⁽¹⁾ | | | 3.6 | V |
| $t_{I2CSTARTUP}$ | Time delay after boot signal on TS1 before I ² C communications allowed | Delay after boot sequence when I ² C communication is allowed | | 1 | | ms |
| $t_{BOOTREADY}$ | Device boot startup delay | Delay after boot signal when device has completed full boot-up sequence | | | 10 | ms |
| T_{SHUTD} | Thermal shutdown voltage | | | 100 | 150 | °C |
| MEASUREMENT SCHEDULE | | | | | | |
| t_{VCELL} | Cell voltage measurement interval | bq76920, bq76930, bq76940 | | 250 | | ms |
| $t_{INDCELL}$ | Individual cell measurement time | Per cell, balancing off | | 50 | | |
| | | Per cell, balancing on | | 12.5 | | |
| t_{CB_RELAX} | Cell balancing relaxation time before cell voltage measured | | | 12.5 | | |
| t_{TEMP_DEC} | Temperature measurement decimation time | Measurement duration for temperature reading | | 12.5 | | |
| t_{BAT} | Pack voltage calculation interval | | | 250 | | |
| t_{TEMP} | Temperature measurement interval | Period of measurement of either TS1/TS2/TS3 or internal die temp | | 2 | | s |
| 14-BIT ADC FOR CELL VOLTAGE AND TEMPERATURE MEASUREMENT | | | | | | |
| ADC_{RANGE} | ADC measurement recommend operation range | V_{CELL} measurements | 2 | | 5 | V |
| | | TS/Temp measurements | 0.3 | | 3 | V |
| ADC_{LSB} | ADC LSB value | | | 382 | | µV |

(1) Measured at BAT pin, rising.

Electrical Characteristics *(continued)*

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with $V_{CELL} = 4$ V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

| PARAMETER | | TEST CONDITION | MIN | TYP | MAX | UNIT |
|-----------|---|--------------------------|-----|-----|-----|------|
| ADC | ADC cell voltage accuracy at 25°C | $V_{CELL} = 3.6 - 4.3$ V | | ±10 | | mV |
| | | $V_{CELL} = 3.2 - 4.6$ V | | ±15 | | |
| | | $V_{CELL} = 2.0 - 5.0$ V | | ±25 | | |
| | ADC cell voltage accuracy 0°C to 60°C | $V_{CELL} = 3.6 - 4.3$ V | | ±20 | | |
| | | $V_{CELL} = 3.2 - 4.6$ V | | ±25 | | |
| | | $V_{CELL} = 2.0 - 5.0$ V | | ±35 | | |
| | ADC cell voltage accuracy –40°C to 85°C | $V_{CELL} = 3.6 - 4.3$ V | –40 | | 40 | |
| | | $V_{CELL} = 3.2 - 4.6$ V | –40 | | 40 | |
| | | $V_{CELL} = 2.0 - 5.0$ V | –50 | | 50 | |

Electrical Characteristics (continued)

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with $V_{CELL} = 4$ V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

| PARAMETER | | TEST CONDITION | MIN | TYP | MAX | UNIT |
|---|--------------------------------|--|--------|--------|--------|----------|
| 16-BIT CC FOR PACK CURRENT MEASUREMENT | | | | | | |
| CC _{RANGE} | CC input voltage range | | –200 | | 200 | mV |
| CC _{FSR} | CC full scale range | | –270 | | 270 | mV |
| CC _{LSB} | CC LSB value | CC running constantly | | 8.44 | | μV |
| t _{CCREAD} | Conversion time | Single conversion | | 250 | | ms |
| CC _{INL} | Integral nonlinearity | 16-bit, best fit over input voltage range ± 200 mV | | ± 2 | ± 40 | LSB |
| CC _{OFFSET} | Offset error | | | ± 1 | ± 3 | LSB |
| CC _{GAIN} | Gain error | Over input voltage range | | ± 0.5% | ± 1.5% | FSR |
| CC _{GAINDRIFT} | Gain error drift | Over input voltage range | | | 150 | PPM / °C |
| CC _{RIN} | Effective input resistance | | | 2.5 | | MΩ |
| THERMISTOR BIAS | | | | | | |
| R _{TS} | Pull-up resistance | T _A = 25°C | 9.85 | 10 | 10.15 | kΩ |
| R _{TS} DRIFT | Pull-up resistance across temp | T _A = –40°C to 85°C | 9.7 | | 10.3 | kΩ |
| DIETEMP | | | | | | |
| V _{DIETEMP25} | Die temperature voltage | T _A = 25°C | | 1.20 | | V |
| V _{DIETEMPDRIFT} | Die temperature voltage drift | | | –4.2 | | mV/°C |
| INTEGRATED HARDWARE PROTECTIONS | | | | | | |
| OV _{RANGE} | OV threshold range | | 0x2008 | | 0x2FF8 | ADC |
| UV _{RANGE} | UV threshold range | | 0x1000 | | 0x1FF0 | ADC |
| OV _{UVSTEP} | OV and UV threshold step size | | | 16 | | LSB |
| UV _{MINQUAL} | UV minimum value to qualify | Below UV _{MINQUAL} , cell is shorted (unused) | | 0x0518 | | ADC |
| OV _{DELAY} | OV delay timer options | OV delay = 1 s | 0.7 | 1 | 1.75 | s |
| | | OV delay = 2 s | 1.6 | 2 | 2.75 | |
| | | OV delay = 4 s | 3.5 | 4 | 5 | |
| | | OV delay = 8 s | 7 | 8 | 10 | |
| UV _{DELAY} | UV delay timer options | UV delay = 1 s | 0.7 | 1 | 1.75 | |
| | | UV delay = 4 s | 3.5 | 4 | 5 | |
| | | UV delay = 8 s | 7 | 8 | 10 | |
| | | UV delay = 16 s | 14 | 16 | 20 | |
| OCD _{RANGE} | OCD threshold options | Measured across (SRP–SRN) ⁽²⁾ | 8 | | 100 | mV |
| OCD _{STEP} | OCD threshold step size | RSNS = 0 | | 2.78 | | mV |
| | | RSNS = 1 | | 5.56 | | mV |
| OCD _{DELAY} | OCD delay options | See Note ⁽³⁾ | 8 | | 1280 | ms |
| SCD _{RANGE} | SCD threshold options | Measured across (SRP–SRN) ⁽²⁾ | 22 | | 200 | mV |
| SCD _{STEP} | SCD threshold step size | RSNS = 0 | | 11.1 | | mV |
| | | RSNS = 1 | | 22.2 | | mV |
| SCD _{DELAY} | SCD delay options | | 35 | 70 | 105 | μs |
| | | | 50 | 100 | 150 | μs |
| | | | 140 | 200 | 260 | μs |
| | | | 280 | 400 | 520 | μs |

(2) Values indicate nominal thresholds only. For Min and Max variation, apply OC_{OFFSET} and OC_{SCALERR}.

(3) Values indicate nominal thresholds only. For Min and Max variation, apply t_{PROTACC}.

Electrical Characteristics *(continued)*

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with $V_{CELL} = 4$ V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

| PARAMETER | | TEST CONDITION | MIN | TYP | MAX | UNIT |
|------------------------------|--|--|---------------|-----------|--------|------|
| t _{PROTACC} | Delay accuracy for OCD | | −20% | | 20% | |
| OC _{OFFSET} | OCD and SCD voltage offset | | −2.5 | | 2.5 | mV |
| OC _{SCALEERR} | OCD and SCD scale accuracy | | −10% | | 10% | |
| CHARGE AND DISCHARGE DRIVERS | | | | | | |
| V _{FETON} | CHG and DSG on | REGSRC ≥ 12 V with load resistance of 10 MΩ | 10 | 12 | 14 | V |
| | | REGSRC < 12 V with load resistance of 10 MΩ | REGSRC −2 | REGSRC −1 | REGSRC | V |
| t _{FET_ON} | CHG and DSG ON rise time | CHG/DSG driving an equivalent load capacitance of 10 nF, measured from 10% to 90% of V _{FETON} | 200 | | 250 | μs |
| t _{DSG_OFF} | DSG pull-down OFF fall time | DSG driving an equivalent load capacitance of 10 nF, measured from 90% to 10% | 60 | | 90 | μs |
| R _{CHG_OFF} | CHG pull-down OFF resistance to VSS | When CHG disabled, CHG held at 12 V | 750 | 1000 | 1250 | kΩ |
| R _{DSG_OFF} | DSG pull-down OFF resistance to VSS | When DSG disabled, DSG held at 12 V | 1.75 | 2.50 | 4.25 | kΩ |
| V _{LOAD_DETECT} | Load detection threshold | | 0.4 | 0.7 | 1.0 | V |
| V _{CHG_CLAMP} | CHG clamp voltage | If the CHG pin externally pulled high (through PACK−, if load applied), 500 μA max sink current into CHG pin. With CHG_ON bit cleared. | 18 | 20 | 22 | V |
| ALERT PIN | | | | | | |
| V _{ALERT_OH} | ALERT output voltage high | I _{OL} = 1 mA | REGOUT x 0.75 | | | V |
| V _{ALERT_OL} | ALERT output voltage low | Unloaded | REGOUT x 0.25 | | | V |
| V _{ALERT_IH} | ALERT input high | ALERT externally forced high when internally driven low. See note ⁽⁴⁾ . | 1 | 1.5 | | V |
| R _{ALERT_PD} | ALERT pin weak pulldown resistance when driven low | Measured into ALERT pin with ALERT = REGOUT | 0.8 | 2.5 | 8 | MΩ |
| CELL BALANCING DRIVER | | | | | | |
| R _{DSFET} | Internal cell balancing driver resistance | V _{CELL} = 3.6 V | 1 | 5 | 10 | Ω |
| X _{BAL} | Cell balancing duty cycle when enabled | Every 250 ms | 70% | | | |
| EXTERNAL REGULATOR | | | | | | |
| V _{EXTLDO} | External LDO voltage options | Nominal values, TI factory programmed, unloaded, across temp | 2.45 | 2.50 | 2.55 | V |
| | | | 3.20 | 3.30 | 3.40 | V |
| V _{EXTLDO_LN} | Line regulation | REGSRC pin stepped from 6 to 25 V, with 10 mA load, in 100 μs | 100 | | | mV |
| V _{EXTLDO_LD} | Load regulation | I _{REGOUT} = 0 mA to 10 mA | −4% | | 4% | |
| V _{EXTLDO_DC} | External LDO minimum voltage under DC load | REGOUT = 10 mA DC, 2.5-V version | 2.4 | | | V |
| | | REGOUT = 20 mA DC, 2.5-V version | 2.3 | | | V |
| | | REGOUT = 10 mA DC, 3.3-V version | 3.15 | | | V |
| | | REGOUT = 20 mA DC, 3.3-V version | 3.05 | | | V |

(4) MIN specifies the threshold below which the device will never register that an external alert has occurred. MAX specifies the minimum threshold above which the device will always register that an external alert has occurred.

Electrical Characteristics (continued)

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with $V_{CELL} = 4$ V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

| PARAMETER | TEST CONDITION | MIN | TYP | MAX | UNIT | | |
|---------------------------|---------------------------------|--|-----|-----|------|------|----|
| I _{EXTLDO_LIMIT} | External LDO current limit | REGOUT = 0 V | 30 | 38 | 45 | mA | |
| BOOT DETECTOR | | | | | | | |
| V _{BOOT} | Boot threshold voltage | Measured at TS1 pin with device in SHIP mode. Below MIN, device will not boot up. Above MAX, device will be guaranteed to boot up. | | | 300 | 1000 | mV |
| t _{BOOT_max} | Boot threshold application time | Measured at TS1 pin. Below MIN, device will not boot up. Above MAX, device will be guaranteed to boot up. | | | 10 | 2000 | μs |

6.6 Timing Requirements

| I²C COMPATIBLE INTERFACE | | MIN | TYP | MAX | UNIT |
|--|--|---------------|-----|---------------|------|
| V_{IL} | Input Low Logic Threshold | | | REGOUT x 0.25 | V |
| V_{IH} | Input High Logic Threshold | REGOUT x 0.75 | | | V |
| V_{OL} | Output Low Logic Drive | | | 0.20 | V |
| t_f | SCL, SDA Fall Time | | | 0.40 | |
| V_{OH} | Output High Logic Drive (Not applicable due to open-drain outputs) | N/A | | N/A | V |
| t_{HIGH} | SCL Pulse Width High | 4.0 | | | μs |
| t_{LOW} | SCL Pulse Width Low | 4.7 | | | μs |
| $t_{SU;STA}$ | Setup time for START condition | 4.7 | | | μs |
| $t_{HD;STA}$ | START condition hold time after which first clock pulse is generated | 4.0 | | | μs |
| $t_{SU;DAT}$ | Data setup time | 250 | | | ns |
| $t_{HD;DAT}$ | Data hold time | 0 | | | μs |
| $t_{SU;STO}$ | Setup time for STOP condition | 4.0 | | | μs |
| t_{BUF} | Time the bus must be free before new transmission can start | 4.7 | | | μs |
| $t_{VD;DAT}$ | Clock Low to Data Out Valid | | | 900 | ns |
| $t_{HD;DAT}$ | Data Out Hold Time After Clock Low | 0 | | | ns |
| f_{SCL} | Clock Frequency | 0 | | 100 | kHz |

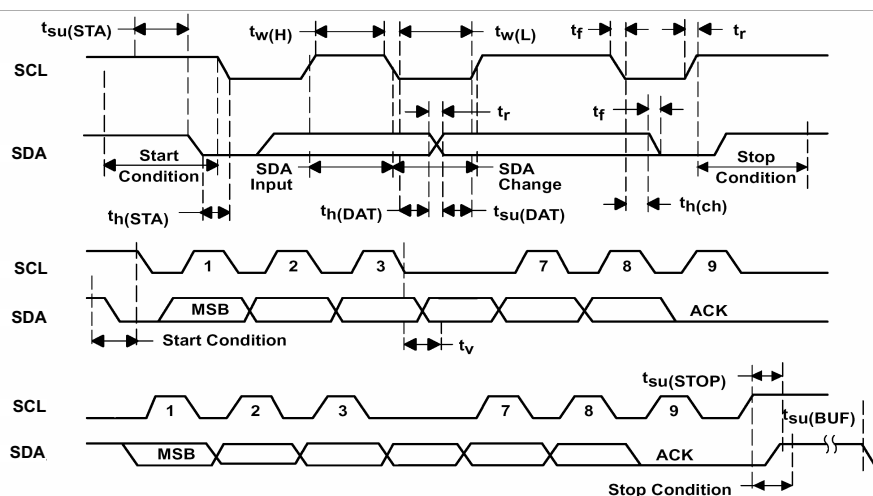


Figure 6-1. I²C Timing

6.7 Typical Characteristics

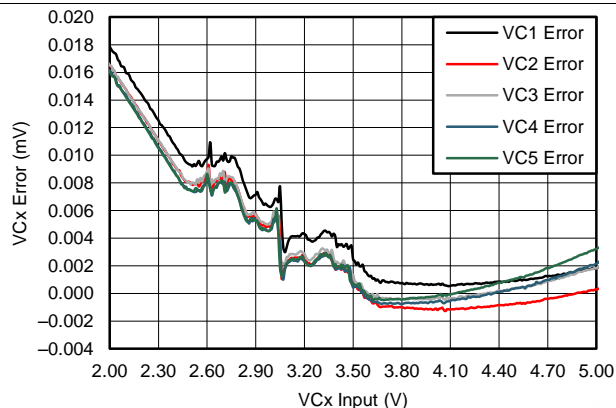


Figure 6-2. bq76930 VCx Error Across Input Range at 25°C with VIN at 3.6 V

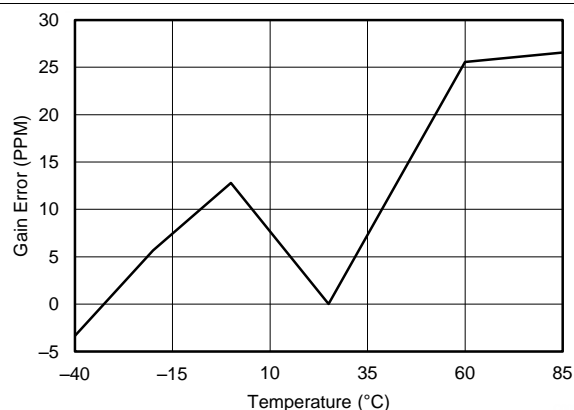


Figure 6-3. Coulomb Counter Gain Error Temperature Drift (from -0.2 V to 0.2 V)

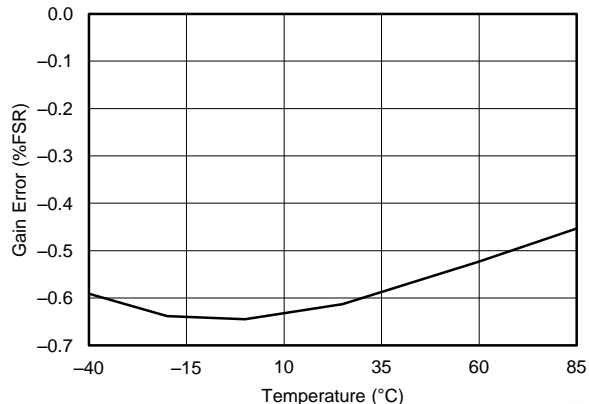


Figure 6-4. Coulomb Counter Gain Error (from -0.2 V to 0.2 V)

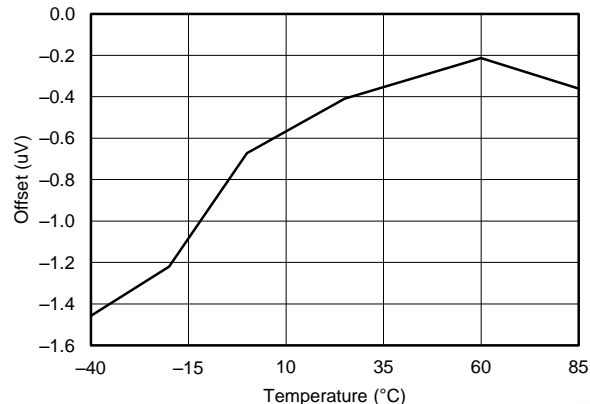


Figure 6-5. Coulomb Counter Offset

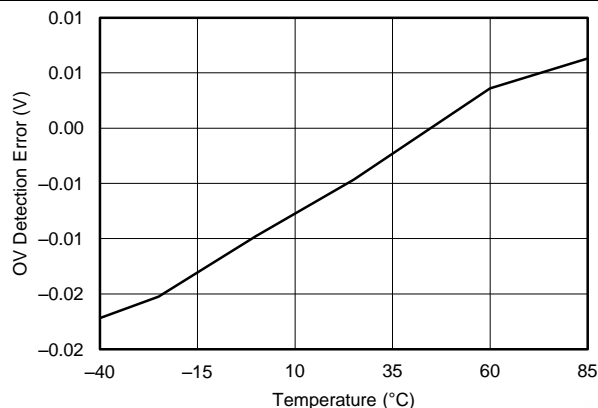


Figure 6-6. OV Protection Detection Error (0xFF Setting)

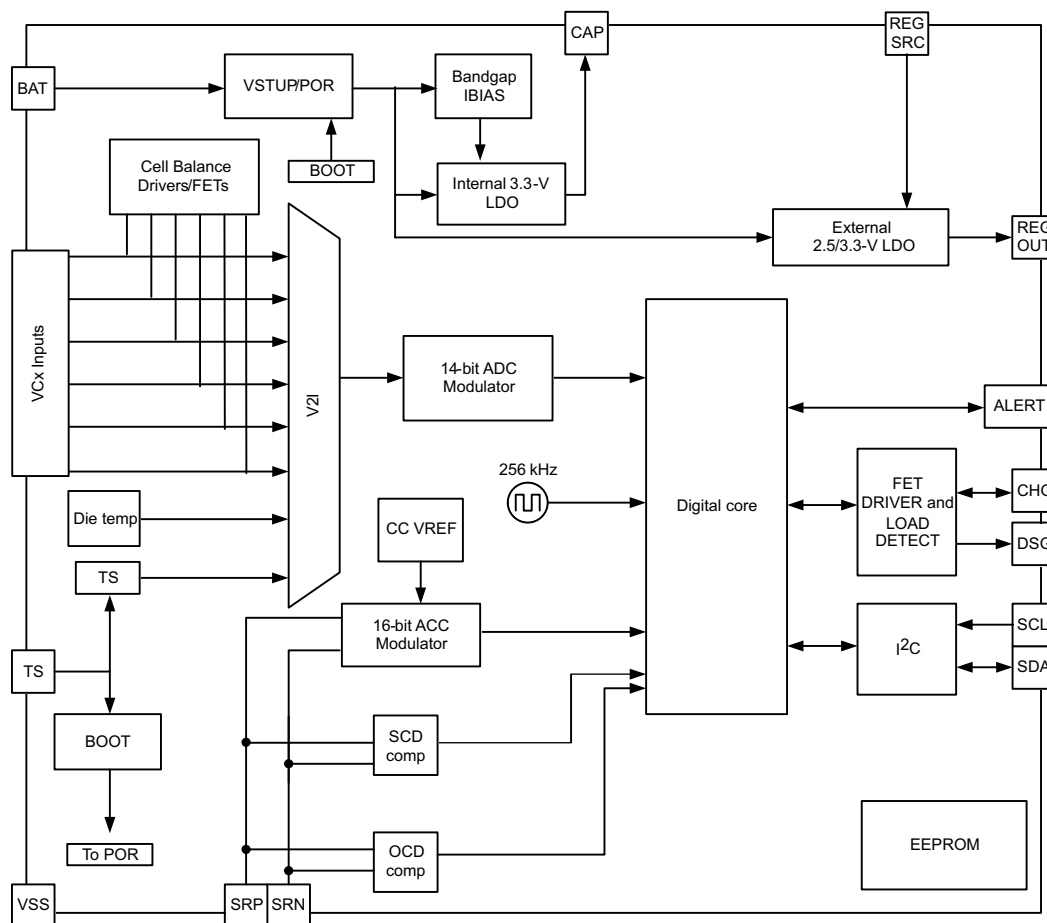
7 Detailed Description

7.1 Overview

In the bq769x0 family of analog front-end (AFE) devices, the bq76920 device supports up to 5-series cells, the bq76930 device supports up to 10-series cells, and the bq76940 device supports up to 15-series cells. through I²C, a host controller can use the bq769x0 to implement battery pack management functions, such as monitoring (cell voltages, pack current, pack temperatures), protection (controlling charge/discharge FETs), and balancing. Integrated A/D converters enable a purely digital readout of critical system parameters including cell voltages and internal or external temperature, with calibration handled in TI's manufacturing process. For an additional degree of pack reliability, the bq769x0 includes hardware protections for voltage (OV, UV) and current (OCD, SCD).

The bq769x0 provides two low-side FET drivers, charge (CHG) and discharge (DSG), which may be used to directly manipulate low-side power NCH FETs, or as signals that control an external circuit that enables high-side PCH or NCH FETs. A dedicated ALERT input/output pin serves as an interrupt signal to the host microcontroller, quickly informing the microcontroller of an updated status in the AFE. This may include a fault event or that a coulomb counter sample is available for reading. An available ALERT pin may also be driven externally by a secondary protector to provide a redundant means of disabling the CHG and DSG signals and higher system visibility.

7.2 Functional Block Diagram



Copyright © 2016, Texas Instruments Incorporated

Figure 7-1. Functional Block Diagram

7.3 Feature Description

7.3.1 Subsystems

bq769x0 consists of three major subsystems: Measurement, Protection, and Control. These work together to ensure that the fundamental battery pack parameters—voltage, current and temperature—are accurately captured and easily available to a host controller, while ensuring a baseline or secondary level of hardware protection in the event that a host controller is unable or unavailable to manage certain fault conditions.

NOTE

The bq769x0 is intended to serve as an analog front-end (AFE) as part of a chipset system solution: A companion microcontroller is required to oversee and control this AFE.

- The Measurement subsystem's core responsibility is to digitize the cell voltages, pack current (integrated into a passed charge calculation), external thermistor temperature, and internal die temperature. It also performs an automatic calculation of the total battery stack voltage, by simply adding up all measured cell voltages.
- The Protection subsystem provides a baseline or secondary level of hardware protections to better support a battery pack's FMEA requirements in the event of a loss of host control or simply if a host is unable to respond to a certain fault event in time. Integrated protections include pack-level faults such as OV, UV, OCD, SCD, detection of an external secondary protector fault, and internal logic "watchdog"-style device fault (XREADY). Protection events will trigger toggling of the ALERT pin, as well as automatic disabling of the DSG and/or CHG FET driver (depending on the fault). Recovery from a fault event must be handled by the host microcontroller.
- The Control subsystem implements a suite of useful pack features, including direct low-side NCH FET drivers, cell balancing drivers, the ALERT digital output, an external LDO and more.

The following sections describe each subsystem in greater detail, as well as explaining the various power states that are available.

7.3.1.1 Measurement Subsystem Overview

The monitoring subsystem ensures that all cell voltages, temperatures, and pack current may be easily measured by the host. All ADCs are trimmed by TI.

ADC and CC data are always returned as atomic values if both high and low registers are read in the same transaction (using address auto-increment).

7.3.1.1.1 Data Transfer to the Host Controller

The bq769x0 has a fully digital interface: All information is transferred through I²C, simply by reading and/or writing to the appropriate register(s) storing the relevant data. Block reads and writes, buffered by an 8-bit CRC code per byte, ensure a fast and robust transmission of data.

7.3.1.1.2 14-Bit ADC

Each bq769x0 device measures cell voltages and temperatures using a 14-bit ADC. This ADC measures all differential cell voltages, thermistors and/or die temperature with a nominal full-scale unsigned range of 0–6.275 V and LSB of 382 μ V.

To enable the ADC, the [ADC_EN] bit in the SYS_CTRL1 register must be set. This bit is set automatically whenever the device enters NORMAL mode. When enabled, the ADC ensures that the integrated OV and UV protections are functional.

For each contiguous set of five cells (VC1 to VC5, VC6 to VC10), when no cells in that particular set are being balanced, each cell is measured over a 50-ms decimation window and a complete update is available every 250 ms. In the bq76930 and bq76940, every set of five cells above the primary five cells is measured in parallel. The 50-ms decimation greatly assists with removing the aliasing effects present in a noisy motor environment.

When any cells in a contiguous set of 5 cells are being balanced, those affected cells are measured in a reduced 12.5-ms decimation period, to allow the cell balancing to function properly without affecting the integrated OV and UV protections. Since cell balancing is typically only performed during pack charge or idle periods, the shortened decimation periods should not impact accuracy as the system noise during these times is greatly reduced. This reduced decimation period is only applied to sets where one of the cells is being balanced. The following summarizes this for the bq76920–bq76940 devices:

- VC1 to VC5 measurements are each taken in a 50-ms decimation period when all bits in CELLBAL1 register are 0, and a 12.5-ms decimation period when any bits in CELLBAL1 register are 1.
- VC6 to VC10 measurements are each taken in a 50-ms decimation period when all bits in CELLBAL2 register are 0, and a 12.5-ms decimation period when any bits in CELLBAL2 register are 1.
- VC11 to VC15 measurements are each taken in a 50-ms decimation period when all bits in CELLBAL3 register are 0, and a 12.5-ms decimation period when any bits in CELLBAL3 register are 1.
- Total update interval is 250 ms.

Each differential cell input is factory-trimmed for gain and/or offset, such that the resulting reading through I²C is always consistent from part-to-part and requires no additional calibration or correction factor application.

The ADC is required to be enabled in order for the integrated OV and UV protections to be operating.

The following shows how to convert the 14-bit ADC reading into an analog voltage. Each device is factory calibrated, with a GAIN and OFFSET stored into EEPROM.

The ADC transfer function is a linear equation defined as follows:

$$V(\text{cell}) = \text{GAIN} \times \text{ADC}(\text{cell}) + \text{OFFSET} \quad (1)$$

GAIN is stored in units of $\mu\text{V}/\text{LSB}$, while OFFSET is stored in mV units.

Some example cell voltage calculations are provided in the table below. For illustration purposes, the example uses a hypothetical GAIN of 380 $\mu\text{V}/\text{LSB}$ (ADCGAIN<4:0> = 0x0F) and OFFSET of 30 mV (ADCOFFSET<7:0> = 0x1E).

| 14-Bit ADC Result | ADC Result in Decimal | GAIN ($\mu\text{V}/\text{LSB}$) | OFFSET (mV) | Cell Voltage (mV) |
|-------------------|-----------------------|-----------------------------------|-------------|-------------------|
| 0x1800 | 6144 | 380 | 30 | 2365 |
| 0x1F10 | 7952 | 380 | 30 | 3052 |

NOTE

When entering NORMAL mode from SHIP mode, please allow for the following times before reading out initial cell voltage data:

bq76920: 250 ms

bq76930: 400 ms

bq76940: 800 ms

7.3.1.1.2.1 Optional Real-time Calibration Using the Host Microcontroller

The performance of the cell voltage values measured by the 14-bit ADC has a factory-calibrated accuracy, as follows:

- ± 10 mV TYP, ± 40 mV MIN and MAX from 3.6 to 4.3 V,
- ± 15 mV TYP, ± 40 mV MIN and MAX from 3.2 to 4.6 V, and
- ± 50 mV MIN and MAX from 2.0 to 5.0 V

While this is suitable for the majority of pack protection and basic monitoring applications the bq769x0 AFE family is intended to support, certain systems may require a higher accuracy performance.

To achieve this, use an available ADC channel and general purpose output terminal on the host microcontroller paired with the bq769x0. A simple external circuit consisting of two precision resistors and a small-signal FET is activated by the host microcontroller to determine the total stack voltage, V_{STACK} . This is then compared against the sum of the individual cell voltages as measured by the internal ADC of the bq769x0. The resulting transfer function coefficient, $GAIN_2$, is simply applied to each cell voltage ADC value for improved accuracy.

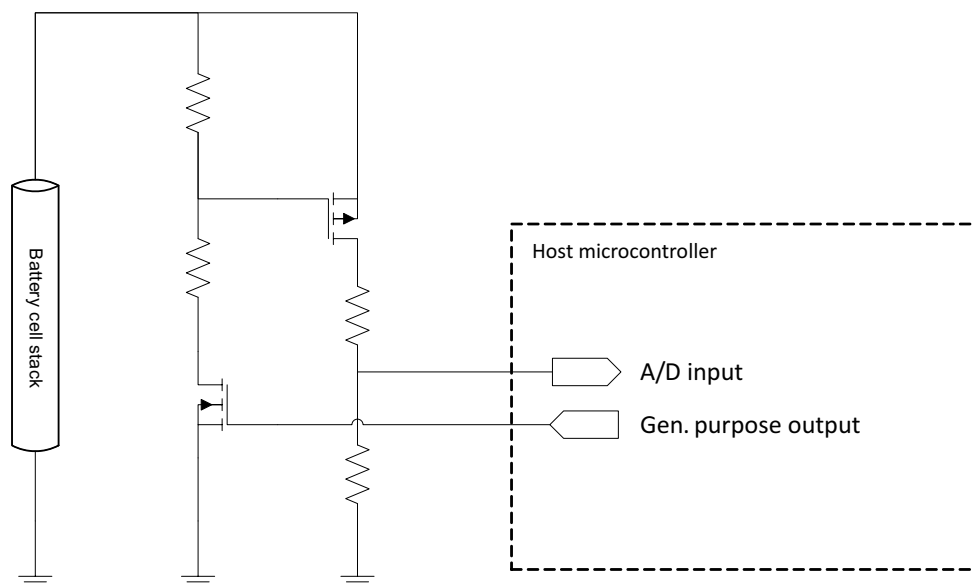


Figure 7-2. External Real-Time Calibration Circuit to Host Microcontroller

The process is as follows:

1. Periodically measure V_{STACK} .
 - (a) $V_{STACK} = V_{AD} \times (R1 + R2) / R1$
2. Read out all V_{CELL} ADC readings from the bq769x0 and apply the standard GAIN and OFFSET values stored in the bq769x0.
 - (a) $V(1) = GAIN \times ADC_1 + OFFSET$, $V(2) = GAIN \times ADC_2 + OFFSET$, and so on
3. Sum up all V_{CELL} values, V_{SUM} .
 - (a) $V_{SUM} = V(1) + V(2) + V(3) \dots$
4. Calculate $GAIN_2$.
 - (a) $GAIN_2 = V_{STACK} / V_{SUM}$

As a general recommendation, a new $GAIN_2$ function should be generated when the cell voltages increase or decrease by more than 100 mV. With $GAIN_2$, each cell voltage calculation becomes:

$$V(\text{cell}) = GAIN_2 \times (GAIN \times ADC(\text{cell}) + OFFSET) \quad (2)$$

For systems that do not require this additional in-use calibration function, $GAIN_2$ is simply "1".

7.3.1.1.3 16-Bit CC

A 16-bit integrating ADC, commonly referred to as the coulomb counter (CC), provides measurements of accumulated charge across the current sense resistor. The integration period for this reading is 250 ms.

The CC may be operated in one of two modes: ALWAYS ON and 1-SHOT.

- In ALWAYS ON mode, the CC runs at 100%, gathering a fresh reading every 250 ms. The conclusion of each reading sets the CC_READY bit, which toggles the ALERT pin high to inform the microcontroller that a new reading is available. To enable Always On mode, set $[CC_EN] = 1$.
- In 1-SHOT mode, the CC performs a single 250-ms reading, and similarly sets the CC_READY bit when completed. This mode is intended for non-gauging usages, where the host simply desires to check the pack current.

To enable a 1-SHOT reading, ensure $[CC_EN] = 0$ and set $[CC_ONESHOT] = 1$.

The full scale range of the CC is ± 270 mV, with a max recommended input range of ± 200 mV, thus yielding an LSB of approximately 8.44 μ V.

The following equation shows how to convert the 16-bit CC reading into an analog voltage if no board-level calibration is performed:

$$\text{CC Reading (in } \mu\text{V)} = [\text{16-bit 2's Complement Value}] \times (8.44 \mu\text{V/LSB}) \quad (3)$$

| 16-Bit CC Result | ADC Result in Decimal | CC Reading (in μ V) |
|------------------|-----------------------|-------------------------|
| 0x0001 | 1 | 8.44 |
| 0x2710 | 10000 | 84,400 |
| 0x7D00 | 32000 | 270,080 |
| 0x8300 | –32000 | –270,080 |
| 0xC350 | –15536 | –131,123.84 |
| 0xFFFF | –1 | –8.44 |

7.3.1.1.4 External Thermistor

One (bq76920), two (bq76930), or three (bq76940) 10 k Ω NTC 103AT thermistors may be measured by the device. These are measured by applying a factory-trimmed internal 10k pull-up resistance to an internal regulator value of nominally 3.3 V, the result of which can be read out from the TSx (TS1, TS2, TS3) registers.

To select thermistor measurement mode, set $[TEMP_SEL] = 1$.

Thermistor TS1 is connected between TS1 and VSS; TS2 is connected between TS2 and VC5x (bq76930 and bq76940 only); and TS3 is connected between TS3 and VC10x (bq76940 only). These thermistors may be placed in various areas in the battery pack to measure such things as localized cell temperature, FET heating, etc.

The thermistor impedance may be calculated using the 14-bit ADC reading in the TS1/TS2/TS3 registers and 10k internal pull-up resistance as follows:

The following equations show how to use the 14-bit ADC readings in TS1, TS2, and TS3 to determine the resistance of the external 103AT thermistor:

$$V_{TSX} = (\text{ADC in Decimal}) \times 382 \mu\text{V/LSB} \quad (4)$$

$$R_{TS} = (10,000 \times V_{TSX}) \div (3.3 - V_{TSX}) \quad (5)$$

To convert the thermistor resistance into temperature, please refer to the thermistor component manufacturer's datasheet.

7.3.1.1.5 Die Temperature Monitor

NOTE

When switching between external and internal temperature monitoring, a 2-s latency may be incurred due to the natural scheduler update interval.

A die temperature block generates a voltage that is proportional to the die temperature, and provides a way of reducing component count if pack thermistors are not used or ensuring that the die power dissipation requirements are observed. The die is measured using the same on-board 14-bit ADC as the cell voltages.

To select internal die temperature measurement mode, set $[TEMP_SEL] = 0$.

For bq76930 and bq76940, multiple die temperature measurements are available. These are stored in TS2 and TS3.

To convert a DIETEMP reading into temperature, refer to the following equation box. If more accurate temperature readings are needed from DIETEMP, the DIETEMP at room temperature value should be stored during production calibration.

The following equation shows how to use the 14-bit ADC readings in TS1, TS2, and TS3 when $[TEMPSEL] = 0$ to determine the internal die temperature:

$$V_{25} = 1.200 \text{ V (nominal)} \quad (6)$$

$$V_{TSX} = (\text{ADC in Decimal}) \times 382 \mu\text{V/LSB} \quad (7)$$

$$TEMP_{DIE} = 25^\circ - ((V_{TSX} - V_{25}) \div 0.0042) \quad (8)$$

7.3.1.1.6 16-Bit Pack Voltage

Once converted to digital form, each cell voltage is added up and the summation result stored in the BAT registers. This 16-bit value has a nominal LSB of 1.532 mV.

The following shows how to convert the 16-bit pack voltage ADC reading into an analog voltage. This value also uses the GAIN and OFFSET stored into EEPROM.

The ADC transfer function is a linear equation defined as follows:

$$V_{(BAT)} = 4 \times \text{GAIN} \times \text{ADC}(\text{cell}) + (\#\text{Cells} \times \text{OFFSET}) \quad (9)$$

GAIN is stored in units of $\mu\text{V/LSB}$, while OFFSET is stored in mV units.

7.3.1.1.7 System Scheduler

A master scheduler oversees the monitoring intervals, creating a full update every 250 ms. Temperature measurements are taken every 2 seconds. Pack voltage is calculated every 250 ms.

7.3.1.2 Protection Subsystem

7.3.1.2.1 Integrated Hardware Protections

Integrated hardware protections are provided as an extra degree of safety and are meant to supplement the standard protection feature set that would be incorporated into the host controller firmware. They should not be used as the sole means of protecting a battery pack, but are useful for FMEA purposes; for example, in the event that a host microcontroller is unable to react to any of the below protection situations. All hardware protection thresholds and delays should be loaded into the AFE by the host microcontroller during system startup. The AFE will also default to pre-defined threshold and delay settings, in case the host microcontroller is unable to or does not wish to program the protection settings.

Overcurrent in Discharge (OCD) and Short Circuit in Discharge (SCD) are implemented using sampled analog comparators that run at 32 kHz, and that continuously monitor the voltage across (SRP–SRN) while the device is in NORMAL mode. Upon detection of a voltage that exceeds the programmed OCD or SCD threshold, a counter begins to count up to a programmed delay setting. If the counter reaches its target value, the SYS_STAT register is updated to indicate the fault condition, the FET state(s) are updated as shown in

[Table 7-1](#), and the ALERT pin is driven high to interrupt the host.

The protection fault threshold and delay settings for OCD and SCD protections are configured through the PROTECT1 and PROTECT2 registers. See [Section 7.5](#) for details about supported values.

Overvoltage (OV) and Undervoltage (UV) protections are handled digitally, by comparing the cell voltage readings against the 8-bit programmed thresholds in the OV and UV registers.

The OV threshold is stored in the OV_TRIP register and is a direct mapping of 8 bits of the 14-bit ADC reading, with the upper 2 MSB preset to “10” and lower 4 LSB preset to “1000”. In other words, the corresponding OV trip level is mapped to “10-XXXX-XXXX-1000”. The programmable range of OV thresholds is approximately 3.15 to 4.7 V, but this is subject to variation due to the (GAIN, OFFSET) linear equation used to map the ADC values.

The UV threshold is stored in the UV_TRIP register and is a direct mapping of 8 bits of the 14-bit ADC reading, with the upper 2 MSB preset to “01” and lower 4 LSB preset to “0000”. In other words, the corresponding UV trip level is mapped to “01-XXXX-XXXX-0000”. The programmable range of UV thresholds is approximately 1.58 to 3.1 V, but this is subject to variation due to the (GAIN, OFFSET) linear equation used to map the ADC values.

| Protection | Upper 2 MSB | Middle 8 Bits | Lower 4 LSB |
|------------|-------------|-------------------------|-------------|
| OV | 10 | Set in OV_TRIP Register | 1000 |
| UV | 01 | Set in UV_TRIP Register | 0000 |

NOTE

To support flexible cell configurations within bq76920, bq76930, and bq76940, UV is ignored on any cells that have a reading under $UV_{MINQUAL}$. This allows cell pins to be shorted in implementations where not all cells are needed (for example, 6-series cells using the bq76930).

Default protection thresholds and delays are shown in the register description at the end of this datasheet. These are loaded into the digital register (RAM) of the device when the device enters NORMAL mode. These RAM values may then be overwritten by the host controller to any other values, which they will retain until a POR event. It is recommended that the host controller reload these values during its standard power-up and/or re-initialization sequence.

To calculate the correct OV_TRIP and UV_TRIP register values for a device, use the following procedure:

1. Determine desired OV.
2. Read out $[ADCGAIN]$ and $[ADCOFFSET]$ from their corresponding registers. Note that ADCGAIN is stored in units of $\mu V/LSB$, while ADCOFFSET is stored in mV.
3. Calculate the full 14-bit ADC value needed to meet the desired OV and UV trip thresholds as follows:
 - (a) $OV_TRIP_FULL = (OV - ADCOFFSET) \div ADCGAIN$
 - (b) $UV_TRIP_FULL = (UV - ADCOFFSET) \div ADCGAIN$
4. Remove the upper 2 MSB and lower 4 LSB from the full 14-bit value, retaining only the remaining middle 8 bits. This can be done by shifting the OV_TRIP_FULL and UV_TRIP_FULL binary values 4 bits to the right and removing the upper 2 MSB.
5. Write OV_TRIP and UV_TRIP to their corresponding registers.

Both OV and UV protections require the ADC to be enabled. Ensure that the `[ADC_EN]` bit is set to 1 if OV and UV protections are needed.

7.3.1.2.2 Reduced Test Time

A special debug and test configuration bit is provided in the SYS_CTRL2 register, called `[DELAY_DIS]`. Setting `[DELAY_DIS]` bypasses the OV/UV protection fault timers and allows a fault condition to be registered within 200 ms after application of such a fault condition.

7.3.1.3 Control Subsystem

7.3.1.3.1 FET Driving (CHG AND DSG)

Each bq769x0 device provides two low-side FET drivers, CHG and DSG, which control NCH power FETs or may be used as a signal to enable various other circuits such as a high-side NCH charge pump circuit.

Both DSG and CHG drivers have a fast pull-up to nominally 12 V when enabled. DSG uses a fast pull-down to VSS when disabled, while CHG utilizes a high impedance (nominally 1 MΩ) pull-down path when disabled.

An additional internal clamp circuit ensures that the CHG pin does not exceed a maximum of 20 V.

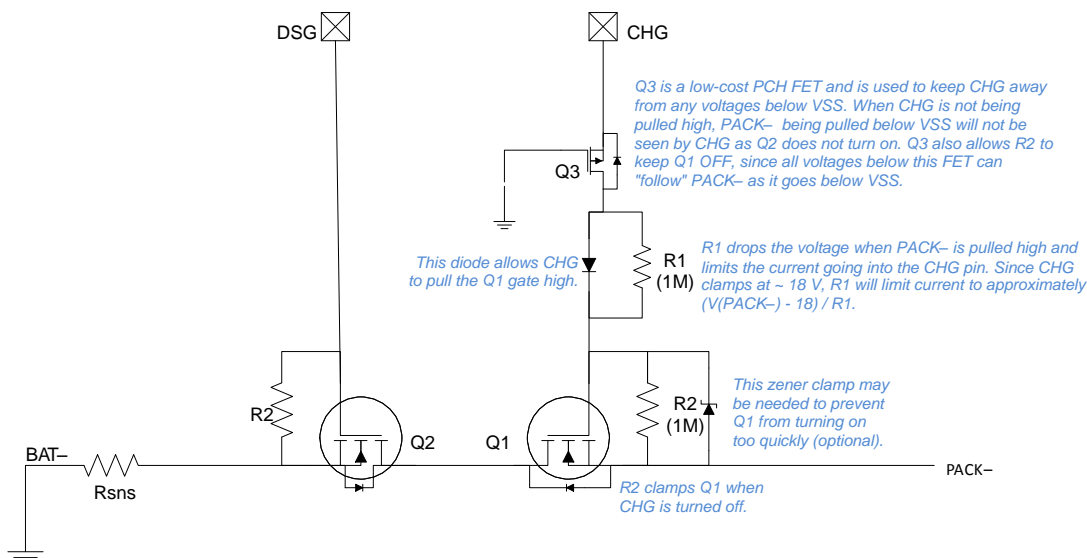


Figure 7-3. CHG and DSG FET Circuit

The power path for the CHG and DSG pull-up circuit originates from the REGSRC pin, instead of BAT.

To enable the CHG fet, set the `[CHG_ON]` register bit to 1; to disable, set `[CHG_ON] = 0`. The discharge FET may be similarly controlled through the `[DSG_ON]` register bit.

Certain fault conditions or power state transitions will clear the state of the CHG/DSG FET controls. Table 7-1 shows what action, if any, to take to `[CHG_ON]` and `[DSG_ON]` in response to various system events:

Table 7-1. CHG, DSG Response Under Various System Events

| EVENT | [CHG_ON] | [DSG_ON] |
|-----------|----------|----------|
| OV Fault | Set to 0 | — |
| UV Fault | — | Set to 0 |
| OCD Fault | — | Set to 0 |

Table 7-1. CHG, DSG Response Under Various System Events (continued)

| EVENT | [CHG_ON] | [DSG_ON] |
|-----------------------------|----------|----------|
| SCD Fault | — | Set to 0 |
| ALERT Override | Set to 0 | Set to 0 |
| DEVICE_XREADY is set | Set to 0 | Set to 0 |
| Enter SHIP mode from NORMAL | Set to 0 | Set to 0 |

NOTE

All protection recovery must be initiated by the host microcontroller. In order to resume FET operation after a fault condition has occurred, the host microcontroller must first clear the corresponding status bit in the SYS_STAT register, which will clear the ALERT pin, and then manually re-enable the CHG and/or DSG bit. Certain faults, such as OV or UV, may immediately re-toggle if such a condition still persists. Refer to [Table 7-3](#) for details on clearing status bits.

There are no conditions under which the bq769x0 automatically sets either [CHG_ON] or [DSG_ON] to 1.

7.3.1.3.2 Load Detection

A load detection circuit is present on the CHG pin and activated whenever the CHG FET is disabled ([CHG_ON] = 0). This circuit detects if the CHG pin is externally pulled high when the high impedance (approximately 1 MΩ) pull-down path should actually be holding the CHG pin to VSS, and is useful for determining if the PACK– pin (outside of the AFE) is being held at a high voltage—for example, if the load is present while the power FETs are off. The state of the load detection circuit is read from the [LOAD_PRESENT] bit of the SYS_CTRL1 register.

After an OCD or SCD fault has occurred, the DSG FET will be disabled ([DSG_ON] cleared), and the CHG FET must similarly be explicitly disabled to activate the load detection circuit. The host microcontroller may periodically poll the [LOAD_PRESENT] bit to determine the state of the PACK– pin and determine when the load is removed ([LOAD_PRESENT] = 0).

7.3.1.3.3 Cell Balancing

Both internal and external passive cell balancing options are fully supported by the bq76920, while external cell balancing is recommended for bq76930 and bq76940. It is left to the host controller to determine the exact balancing algorithm to be used in any given system. Each bq769x0 device provides the cell voltages and balancing drivers to enable this. If using the internal cell balance drivers, up to 50 mA may be balanced per cell. If using external cell balancing, much higher balancing currents may be employed.

To activate a particular cell balancing channel, simply set the corresponding bit for that cell in the CELLBAL1, CELLBAL2, or CELLBAL3 register. For example, VC1–VC0 is enabled by setting [CB1], while VC12–VC11 is set through [CB12].

Multiple cells may be simultaneously balanced. It is left to the user's discretion to determine the ideal number of cells to concurrently balance. Adjacent cells should not be balanced simultaneously. This may cause cell pins to exceed their absolute maximum conditions and is also not recommended for external balancing implementations. Additionally, if internal balancing is used, care should be taken to avoid exceeding package power dissipation ratings.

NOTE

The host controller must ensure that no two adjacent cells are balanced simultaneously within each set of the following:

- VC1–VC5
- VC6–VC10
- VC11–VC15

The total duty cycle devoted to balancing is approximately 70% per 250 ms. This is because a portion of the 250 ms is allotted for normal cell voltage measurements through the ADC.

If $[ADC_EN] = 1$, OV and UV protections are not affected by cell balancing, since the cell balancing is temporarily suspended for a small slice of time every 250 ms during which the cell voltage readings are taken. This ensures that the OV and UV protections do not accidentally trigger, or miss an actual OV/UV condition on the cells while balancing is enabled.

NOTE

All cell balancing control bits in CELLBAL1, CELLBAL2, and CELLBAL3 are automatically cleared under the following events, and must be explicitly re-written by the host microcontroller following clearing of the event:

- DEVICE_XREADY is set
- Enters NORMAL mode from SHIP mode

7.3.1.3.4 Alert

The ALERT pin serves as an active high digital interrupt signal that can be connected to a GPIO port of the host microcontroller. This signal is an OR of all bits in the SYS_STAT register.

In order to clear the ALERT signal, the source bit in the SYS_STAT register must first be cleared by writing a “1” to that bit. This will cause an automatic clear of the ALERT pin once all bits are cleared.

The ALERT pin may also be driven by an external source; for example, the pack may include a secondary overvoltage protector IC. When the ALERT pin is forced high externally while low, the device will recognize this as an OVRD_ALERT fault and set the $[OVRD_ALERT]$ bit. This triggers automatic disabling of both CHG and DSG FET drivers. The device cannot recognize the ALERT signal input high when it is already forcing the ALERT signal high from another condition.

The ALERT pin has no internal debounce support so care should be taken to protect the pin from noise or other parasitic transients.

NOTE

It is highly recommended to place an external 500 k Ω –1 M Ω pull-down resistor from ALERT to VSS as close to the IC as possible. Additional recommendations are:

- a) To keep all traces between the IC and components connected to the ALERT pin very short.
- b) To include a guard ring around the components connected to the ALERT pin and the pin itself.

7.3.1.3.5 Output LDO

An adjustable output voltage regulator LDO is provided as a simple way to provide power to additional components in the battery pack, such as the host microcontroller or LEDs. The LDO is configured in EEPROM by TI during the production test process, and can support 2.5-V or 3.3-V options.

A cascode small-signal FET must be added in the external path between BAT and REGSRC with the bq76930 and bq76940. This helps drop most of the power dissipation outside of the package and cuts down on package power dissipation.

7.3.1.4 Communications Subsystem

The AFE implements a standard 100-kHz I²C interface and acts as a slave device. The I²C device address is 7-bits and is factory programmed. Consult the Device Comparison Table (Section 4) of this datasheet for more information.

A write transaction is shown in Figure 7-4. Block writes are allowed by sending additional data bytes before the Stop. The I²C block will auto-increment the register address after each data byte.

When enabled, the CRC is calculated as follows:

- In a single-byte write transaction, the CRC is calculated over the slave address, register address, and data.
- In a block write transaction, the CRC for the first data byte is calculated over the slave address, register address, and data. The CRC for subsequent data bytes is calculated over the data byte only.

The CRC polynomial is $x^8 + x^2 + x + 1$, and the initial value is 0.

When the slave detects a bad CRC, the I²C slave will NACK the CRC, which causes the I²C slave to go to an idle state.

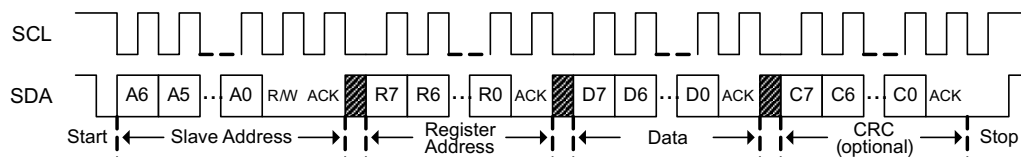


Figure 7-4. I²C Write

Figure 7-5 shows a read transaction using a Repeated Start.

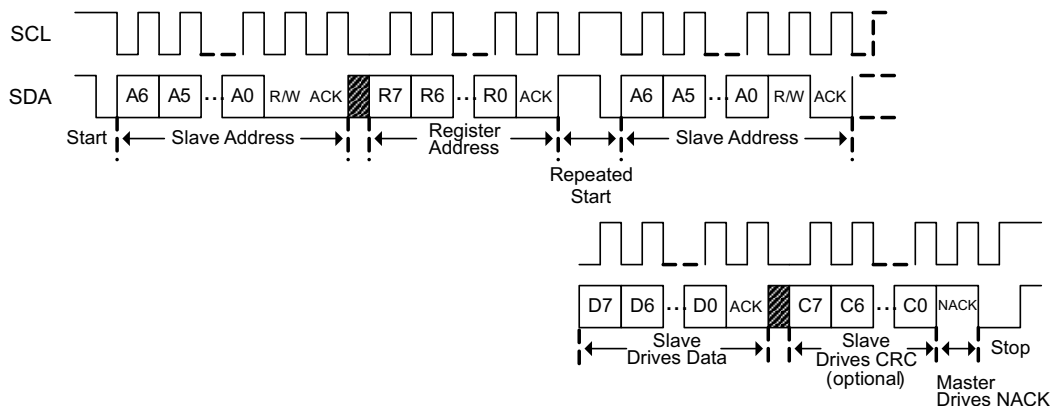


Figure 7-5. I²C Read with Repeated Start

Figure 7-6 shows a read transaction where a Repeated Start is not used, for example if not available in hardware. For a block read, the master ACK's each data byte except the last and continues to clock the interface. The I²C block will auto-increment the register address after each data byte.

When enabled, the CRC for a read transaction is calculated as follows:

- In a single-byte read transaction, the CRC is calculated after the second start and uses the slave address and data byte.

- In a block read transaction, the CRC for the first data byte is calculated after the second start and uses the slave address and data byte. The CRC for subsequent data bytes is calculated over the data byte only.

The CRC polynomial is $x^8 + x^2 + x + 1$, and the initial value is 0.

When the master detects a bad CRC, the I²C master will NACK the CRC, which causes the I²C slave to go to an idle state.

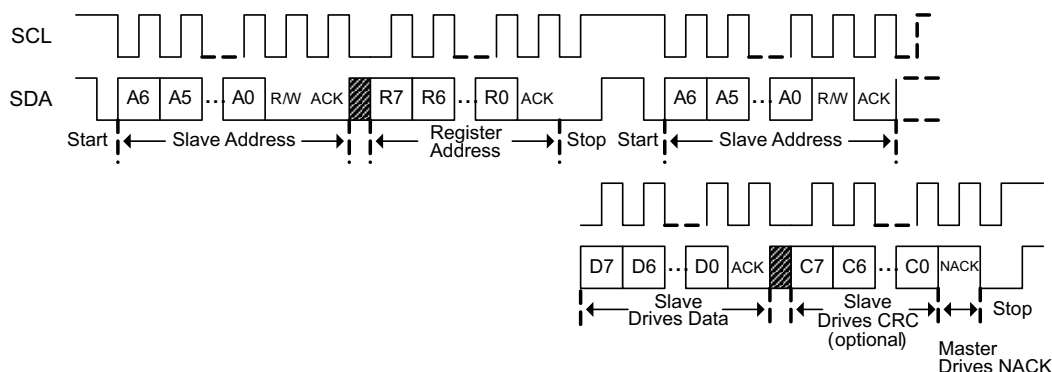


Figure 7-6. I²C Read Without Repeated Start

7.4 Device Functional Modes

Each bq769x0 device supports the following modes of operation.

Table 7-2. Supported Power Modes

| Mode | Description |
|--------|--|
| NORMAL | Fully operational state. Both ADC and CC may be on, or disabled by host microcontroller. OV and UV protection enabled if ADC is on. OCD and SCD enabled. ADC and CC may be disabled to reduce power consumption, and CC may be operated in a "1-SHOT" mode for flexible power savings. |
| SHIP | Lowest possible power state, intended for pack assembly and/or long term pack storage. Must see a BOOT signal (> 1 VBOOT) on TS1 pin to boot from SHIP → NORMAL. Note that the device always enters SHIP mode upon POR. |

7.4.1 NORMAL Mode

NORMAL mode represents the fully operational mode where all blocks are enabled and the device sees its highest current consumption. In this mode, certain blocks/functions may be disabled to save power—these include the ADC and CC. OV and UV are running continuously as long as the ADC is enabled. The OCD and SCD comparators may not be disabled in this mode.

Transitioning from NORMAL to SHIP mode is also initiated by the host, and requires consecutive writes to two bits in the SYS_CTRL1 register.

7.4.2 SHIP Mode

SHIP mode is the basic and lowest power mode that bq769x0 supports. SHIP mode is automatically entered during initial pack assembly and after every POR event. When the device is in NORMAL mode, it may enter SHIP by the host controller through a specific sequence of I²C commands.

In SHIP mode, only a minimum of blocks are turned on, including the VSTUP power supply and primal boot detector. Waking from SHIP mode to NORMAL mode requires pulling the TS1 pin greater than VBOOT, which triggers the device boot-up sequence.

To enter SHIP mode from NORMAL mode, the $[SHUT_A]$ and $[SHUT_B]$ bits in the SYS_CTRL1 register must be written with specific patterns across two consecutive writes:

- Write #1: $[SHUT_A] = 0$, $[SHUT_B] = 1$
- Write #2: $[SHUT_A] = 1$, $[SHUT_B] = 0$

Note that $[SHUT_A]$ and $[SHUT_B]$ should each be in a 0 state prior to executing the shutdown command above. If this specific sequence is entered into the device, the device transitions into SHIP mode. If any other sequence is written to the $[SHUT_A]$ and $[SHUT_B]$ bits or if either of the two patterns is not correctly entered, the device will not enter SHIP mode.

CAUTION

DO NOT OPERATE THE DEVICE BELOW POR. When designing with the bq76940, the intermediate voltages (BAT–VC10x), (VC10x–VC5x), and (VC5x–VSS) must each never fall below V_{SHUT} . When this occurs, a full device reset must be initiated by powering down all three intermediate voltages (BAT–VC10x), (VC10x–VC5x), and (VC5x–VSS) below V_{SHUT} and rebooting by applying the appropriate VBOOT signal to the TS1 pin. When designing with the bq76930, the intermediate voltages (BAT–VC5x) and (VC5x–VSS) must each never fall below V_{SHUT} . If this occurs, a full device reset must be initiated by powering down both intermediate voltages (BAT–VC5x) and (VC5x–VSS) below V_{SHUT} and rebooting by applying the appropriate VBOOT signal to the TS1 pin.

The device will also enter SHIP mode during a POR event; however, this is not a recommended method of SHIP mode entry. If any of the supply-side voltages below fall below V_{SHUT} and then back up above VPORA, the device defaults into the SHIP mode state. This is similar to an initial pack assembly condition. In order to exit SHIP mode into NORMAL mode, the device must follow the standard boot sequence by applying a voltage greater than the VBOOT threshold on the TS1 pin.

7.5 Register Maps

| Name | Addr | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 |
|-------------------------|------|--------------|-----------|----------------------------|------------|------------|------------|--------|--------|
| SYS_STAT | 0x00 | CC_READY | RSVD | DEVICE_XREADY | OVRD_ALERT | UV | OV | SCD | OCD |
| CELLBAL1 | 0x01 | RSVD | RSVD | RSVD | CB<5:1> | | | | |
| CELLBAL2 ⁽¹⁾ | 0x02 | RSVD | RSVD | RSVD | CB<10:6> | | | | |
| CELLBAL3 ⁽²⁾ | 0x03 | RSVD | RSVD | RSVD | CB<15:11> | | | | |
| SYS_CTRL1 | 0x04 | LOAD_PRESENT | RSVD | RSVD | ADC_EN | TEMP_SEL | RSVD | SHUT_A | SHUT_B |
| SYS_CTRL2 | 0x05 | DELAY_DIS | CC_EN | CC_ONESHOT | RSVD | | | DSG_ON | CHG_ON |
| PROTECT1 | 0x06 | RSNS | RSVD | RSVD | SCD_DELAY | | SCD_THRESH | | |
| PROTECT2 | 0x07 | RSVD | OCD_DELAY | | | OCD_THRESH | | | |
| PROTECT3 | 0x08 | UV_DELAY | | OV_DELAY | | RSVD | | | |
| OV_TRIP | 0x09 | OV_THRESH | | | | | | | |
| UV_TRIP | 0x0A | UV_THRESH | | | | | | | |
| CC_CFG | 0x0B | RSVD | RSVD | Must be programmed to 0x19 | | | | | |
| VC1_HI | 0x0C | RSVD | RSVD | <13:8> | | | | | |
| VC1_LO | 0x0D | <7:0> | | | | | | | |
| VC2_HI | 0x0E | RSVD | RSVD | <13:8> | | | | | |
| VC2_LO | 0x0F | <7:0> | | | | | | | |
| VC3_HI | 0x10 | RSVD | RSVD | <13:8> | | | | | |
| VC3_LO | 0x11 | <7:0> | | | | | | | |
| VC4_HI | 0x12 | RSVD | RSVD | <13:8> | | | | | |
| VC4_LO | 0x13 | <7:0> | | | | | | | |
| VC5_HI | 0x14 | RSVD | RSVD | <13:8> | | | | | |
| VC5_LO | 0x15 | <7:0> | | | | | | | |
| VC6_HI ⁽¹⁾ | 0x16 | RSVD | RSVD | <13:8> | | | | | |
| VC6_LO ⁽¹⁾ | 0x17 | <7:0> | | | | | | | |
| VC7_HI ⁽¹⁾ | 0x18 | RSVD | RSVD | <13:8> | | | | | |
| VC7_LO ⁽¹⁾ | 0x19 | <7:0> | | | | | | | |
| VC8_HI ⁽¹⁾ | 0x1A | RSVD | RSVD | <13:8> | | | | | |
| VC8_LO ⁽¹⁾ | 0x1B | <7:0> | | | | | | | |
| VC9_HI ⁽¹⁾ | 0x1C | RSVD | RSVD | <13:8> | | | | | |
| VC9_LO ⁽¹⁾ | 0x1D | <7:0> | | | | | | | |
| VC10_HI ⁽¹⁾ | 0x1E | RSVD | RSVD | <13:8> | | | | | |
| VC10_LO ⁽¹⁾ | 0x1F | <7:0> | | | | | | | |
| VC11_HI ⁽²⁾ | 0x20 | RSVD | RSVD | <13:8> | | | | | |
| VC11_LO ⁽²⁾ | 0x21 | <7:0> | | | | | | | |
| VC12_HI ⁽²⁾ | 0x22 | RSVD | RSVD | <13:8> | | | | | |
| VC12_LO ⁽²⁾ | 0x23 | <7:0> | | | | | | | |
| VC13_HI ⁽²⁾ | 0x24 | RSVD | RSVD | <13:8> | | | | | |
| VC13_LO ⁽²⁾ | 0x25 | <7:0> | | | | | | | |
| VC14_HI ⁽²⁾ | 0x26 | RSVD | RSVD | <13:8> | | | | | |
| VC14_LO ⁽²⁾ | 0x27 | <7:0> | | | | | | | |
| VC15_HI ⁽²⁾ | 0x28 | RSVD | RSVD | <13:8> | | | | | |
| VC15_LO ⁽²⁾ | 0x29 | <7:0> | | | | | | | |
| BAT_HI | 0x2A | <15:8> | | | | | | | |
| BAT_LO | 0x2B | <7:0> | | | | | | | |
| TS1_HI | 0x2C | RSVD | RSVD | <13:8> | | | | | |
| TS1_LO | 0x2D | <7:0> | | | | | | | |
| TS2_HI ⁽¹⁾ | 0x2E | RSVD | RSVD | <13:8> | | | | | |
| TS2_LO ⁽¹⁾ | 0x2F | <7:0> | | | | | | | |

(1) These registers are only valid for bq76930 and bq76940.

(2) These registers are only valid for bq76940.

| Name | Addr | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 |
|-----------------------|------|----------------|------|--------|------|--------------|----|------|----|
| TS3_HI ⁽²⁾ | 0x30 | RSVD | RSVD | <13:8> | | | | | |
| TS3_LO ⁽²⁾ | 0x31 | <7:0> | | | | | | | |
| CC_HI | 0x32 | <15:8> | | | | | | | |
| CC_LO | 0x33 | <7:0> | | | | | | | |
| ADCGAIN1 | 0x50 | RSVD | | | | ADCGAIN<4:3> | | RSVD | |
| ADCOFFSET | 0x51 | ADCOFFSET<7:0> | | | | | | | |
| ADCGAIN2 | 0x59 | ADCGAIN<2:0> | | | RSVD | | | | |

7.5.1 Register Details

Table 7-3. SYS_STAT (0x00)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|----------|------|---------------|------------|----|----|-----|-----|
| NAME | CC_READY | RSVD | DEVICE_XREADY | OVRD_ALERT | UV | OV | SCD | OCD |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | RW | RW | RW | RW | RW | RW | RW | RW |

NOTE

Bits in SYS_STAT may be cleared by writing a "1" to the corresponding bit.

Writing a "0" does not change the state of the corresponding bit.

CC_READY (Bit 7): Indicates that a fresh coulomb counter reading is available. Note that if this bit is not cleared between two adjacent CC readings becoming available, the bit remains latched to 1. This bit may only be cleared (and not set) by the host.

0 = Fresh CC reading not yet available or bit is cleared by host microcontroller.

1 = Fresh CC reading is available. Remains latched high until cleared by host.

RSVD (Bit 6): Reserved. Do not use.

DEVICE_XREADY (Bit 5): Internal chip fault indicator. When this bit is set to 1, it should be cleared by the host. May be set due to excessive system transients. This bit may only be cleared (and not set) by the host.

0 = Device is OK.

1 = Internal chip fault detected, recommend that host microcontroller clear this bit after waiting a few seconds. Remains latched high until cleared by the host.

OVRD_ALERT (Bit 4): External pull-up on the ALERT pin indicator. Only active when ALERT pin is not already being driven high by the AFE itself.

0 = No external override detected

1 = External override detected. Remains latched high until cleared by the host.

UV (Bit 3): Undervoltage fault event indicator.

0 = No UV fault is detected.

1 = UV fault is detected. Remains latched high until cleared by the host.

OV (Bit 2): Overvoltage fault event indicator.

0 = No OV fault is detected.

1 = OV fault is detected. Remains latched high until cleared by the host.

SCD (Bit 1): Short circuit in discharge fault event indicator.

0 = No SCD fault is detected.

1 = SCD fault is detected. Remains latched high until cleared by the host.

OCD (Bit 0): Over current in discharge fault event indicator.

0 = No OCD fault is detected.

1 = OCD fault is detected. Remains latched high until cleared by the host.

Table 7-4. CELLBAL1 (0x01) for bq76920, bq76930, and bq76940

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|---|---|---|-----|-----|-----|-----|-----|
| NAME | — | — | — | CB5 | CB4 | CB3 | CB2 | CB1 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | R | R | R | RW | RW | RW | RW | RW |

CBx (Bits 4–0):

0 = Cell balancing on Cell “x” is disabled.

1 = Cell balancing on Cell “x” is enabled.

Table 7-5. CELLBAL2 (0x02) for bq76930 and bq76940

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|---|---|---|------|-----|-----|-----|-----|
| NAME | — | — | — | CB10 | CB9 | CB8 | CB7 | CB6 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | R | R | R | RW | RW | RW | RW | RW |

CBx (Bits 4–0):

0 = Cell balancing on Cell “x” is disabled.

1 = Cell balancing on Cell “x” is enabled.

Table 7-6. CELLBAL3 (0x03) for bq76940

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|---|---|---|------|------|------|------|------|
| NAME | — | — | — | CB15 | CB14 | CB13 | CB12 | CB11 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | R | R | R | RW | RW | RW | RW | RW |

CBx (Bits 4–0):

0 = Cell balancing on Cell “x” is disabled.

1 = Cell balancing on Cell “x” is enabled.

Table 7-7. SYS_CTRL1 (0x04)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|--------------|---|---|--------|----------|------|--------|--------|
| NAME | LOAD_PRESENT | — | — | ADC_EN | TEMP_SEL | RSVD | SHUT_A | SHUT_B |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | R | R | R | RW | RW | RW | RW | RW |

LOAD_PRESENT (Bit 7): Valid only when [CHG_ON] = 0. Is high if CHG pin is detected to exceed VLOAD_DETECT while CHG_ON = 0, which suggests that external load is present. Note this bit is read-only and automatically clears when load is removed.

0 = CHG pin < VLOAD_DETECT or [CHG_ON] = 1.

1 = CHG pin > VLOAD_DETECT, while [CHG_ON] = 0.

ADC_EN (Bit 4): ADC enable command

0 = Disable voltage and temperature ADC readings (also disables OV protection)

1 = Enable voltage and temperature ADC readings (also enables OV protection)

TEMP_SEL (Bit 3): TSx_HI and TSx_LO temperature source

0 = Store internal die temperature voltage reading in TSx_HI and TSx_LO

1 = Store thermistor reading in TSx_HI and TSx_LO (all thermistor ports)

RSVD (Bit 2): Reserved, do not set to 1.

SHUT_A, SHUT_B (Bits 1–0): Shutdown command from host microcontroller. Must be written in a specific sequence, shown below:

Starting from: [SHUT_A] = 0, [SHUT_B] = 0

Write #1: [SHUT_A] = 0, [SHUT_B] = 1

Write #2: [SHUT_A] = 1, [SHUT_B] = 0

Other writes cause the command to be ignored.

Table 7-8. SYS_CTRL2 (0x05)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|-----------|-------|------------|------|------|------|--------|--------|
| NAME | DELAY_DIS | CC_EN | CC_ONESHOT | RSVD | RSVD | RSVD | DSG_ON | CHG_ON |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | RW | RW | RW | RW | RW | RW | RW | RW |

DELAY_DIS (Bit 7): Disable OV, UV, OCD, and SCD delays for faster customer production testing.

0 = Normal delay settings

1 = OV, UV, OCD, and SCD delay circuit is bypassed, creating zero delay (approximately 250 ms).

CC_EN (Bit 6): Coulomb counter continuous operation enable command. If set high, [CC_ONESHOT] bit is ignored.

0 = Disable CC continuous readings

1 = Enable CC continuous readings and ignore [CC_ONESHOT] state

CC_ONESHOT (Bit 5): Coulomb counter single 250-ms reading trigger command. If set to 1, the coulomb counter will be activated for a single 250-ms reading, and then turned back off.

[CC_ONESHOT] will also be cleared at the conclusion of this reading, while [CC_READY] bit will be set to 1.

0 = No action

1 = Enable single CC reading (only valid if [CC_EN] = 0), and [CC_READY] = 0)

RSVD (Bit 4–2): Reserved. Do not use.

DSG_ON (Bit 1): Discharge FET driver (low side NCH) or discharge signal control

0 = DSG is off.

1 = DSG is on.

CHG_ON (Bit 0): Discharge FET driver (low side NCH) or discharge signal control

0 = CHG is off.

1 = CHG is on.

Table 7-9. PROTECT1 (0x06)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|------|---|------|--------|--------|--------|--------|--------|
| NAME | RSNS | — | RSVD | SCD_D1 | SCD_D0 | SCD_T2 | SCD_T1 | SCD_T0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | RW | R | RW | RW | RW | RW | RW | RW |

RSNS (Bit 7): Allows for doubling the OCD and SCD thresholds simultaneously

0 = OCD and SCD thresholds at lower input range

1 = OCD and SCD thresholds at upper input range

RSVD (Bit 5): Reserved, do not set to 1.

SCD_D1:0 (Bits 4–3):

Short circuit in discharge delay setting. A 400- μ s setting is recommended only in systems using maximum cell measurement input resistance, R_c , of 1 k Ω (which corresponds to minimum internal cell balancing current or external cell balancing configuration).

| Code | (in μ s) |
|------|--------------|
| 0x0 | 70 |
| 0x1 | 100 |
| 0x2 | 200 |
| 0x3 | 400 |

SCD_T2:0 (Bits 2–0): Short circuit in discharge threshold setting

| Code | RSNS = 1 (in mV) | RSNS = 0 (in mV) |
|------|------------------|------------------|
| 0x0 | 44 | 22 |
| 0x1 | 67 | 33 |
| 0x2 | 89 | 44 |
| 0x3 | 111 | 56 |
| 0x4 | 133 | 67 |
| 0x5 | 155 | 78 |
| 0x6 | 178 | 89 |
| 0x7 | 200 | 100 |

Table 7-10. PROTECT2 (0x07)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|---|--------|--------|--------|--------|--------|--------|--------|
| NAME | — | OCD_D2 | OCD_D1 | OCD_D0 | OCD_T3 | OCD_T2 | OCD_T1 | OCD_T0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | R | RW | RW | RW | RW | RW | RW | RW |

OCD_D2:0 (Bits 6–4): Overcurrent in discharge delay setting

| Code | (in ms) |
|------|---------|
| 0x0 | 8 |
| 0x1 | 20 |
| 0x2 | 40 |
| 0x3 | 80 |
| 0x4 | 160 |
| 0x5 | 320 |
| 0x6 | 640 |
| 0x7 | 1280 |

OCD_T3:0 (Bits 3–0): Overcurrent in discharge threshold setting.

| Code | RSNS = 1 (in mV) | (RSNS = 0 (in mV)) |
|------|------------------|--------------------|
| 0x0 | 17 | 8 |
| 0x1 | 22 | 11 |
| 0x2 | 28 | 14 |
| 0x3 | 33 | 17 |
| 0x4 | 39 | 19 |
| 0x5 | 44 | 22 |
| 0x6 | 50 | 25 |
| 0x7 | 56 | 28 |
| 0x8 | 61 | 31 |
| 0x9 | 67 | 33 |
| 0xA | 72 | 36 |
| 0xB | 78 | 39 |
| 0xC | 83 | 42 |
| 0xD | 89 | 44 |
| 0xE | 94 | 47 |
| 0xF | 100 | 50 |

Table 7-11. PROTECT3 (0x08)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|-------|-------|-------|-------|------|------|------|------|
| NAME | UV_D1 | UV_D0 | OV_D1 | OV_D0 | RSVD | RSVD | RSVD | RSVD |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | RW | RW | RW | RW | RW | RW | RW | RW |

UV_D1:0 (Bits 7–6): Undervoltage delay setting

| Code | (in s) |
|------|--------|
| 0x0 | 1 |
| 0x1 | 4 |
| 0x2 | 8 |
| 0x3 | 16 |

OV_D1:0 (Bits 5–4): Overvoltage delay setting

| Code | (in s) |
|------|--------|
| 0x0 | 1 |
| 0x1 | 2 |
| 0x2 | 4 |
| 0x3 | 8 |

RSVD (Bits 3–0): These bits are for TI internal debug use only and must be configured to the default settings indicated.

Table 7-12. OV_TRIP (0x09)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|-------|-------|-------|-------|-------|-------|-------|-------|
| NAME | OV_T7 | OV_T6 | OV_T5 | OV_T4 | OV_T3 | OV_T2 | OV_T1 | OV_T0 |
| RESET | 1 | 0 | 1 | 0 | 1 | 1 | 0 | 0 |
| ACCESS | RW | RW | RW | RW | RW | RW | RW | RW |

OV_T7:0 (Bits 7–0): Middle 8 bits of the direct ADC mapping of the desired OV protection threshold, with upper 2 MSB set to 10 and lower 2 LSB set to 1000. The equivalent OV threshold is mapped to: 10-OV_T<7:0>1000.

By default, OV_TRIP is configured to a 0xAC setting.

Note that OV_TRIP is based on the ADC voltage, which requires back-calculation using the GAIN and OFFSET values stored in ADCGAIN<4:0>and ADCOFFSET<7:0>.

Table 7-13. UV_TRIP (0x0A)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|-------|-------|-------|-------|-------|-------|-------|-------|
| NAME | UV_T7 | UV_T6 | UV_T5 | UV_T4 | UV_T3 | UV_T2 | UV_T1 | UV_T0 |
| RESET | 1 | 0 | 0 | 1 | 0 | 1 | 1 | 1 |
| ACCESS | RW | RW | RW | RW | RW | RW | RW | RW |

UV_T7:0 (Bits 7–0): Middle 8 bits of the direct ADC mapping of the desired UV protection threshold, with upper 2 MSB set to 01 and lower 4 LSB set to 0000. In other words, the equivalent OV threshold is mapped to: 01-UV_T<7:0>–0000.

By default, UV_TRIP is configured to a 0x97 setting. .

Note that UV_TRIP is based on the ADC voltage, which requires back-calculation using the GAIN and OFFSET values stored in ADCGAIN<4:0>and ADCOFFSET<7:0>.

Table 7-14. CC_CFG REGISTER (0x0B)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|---|---|---------|---------|---------|---------|---------|---------|
| NAME | — | — | CC_CFG5 | CC_CFG4 | CC_CFG3 | CC_CFG2 | CC_CFG1 | CC_CFG0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| ACCESS | R | R | RW | RW | RW | RW | RW | RW |

CC_CFG5:0 (Bits 5–0): For optimal performance, these bits should be programmed to 0x19 upon device startup.

7.5.2 Read-Only Registers

Table 7-15. CELL VOLTAGE REGISTERS

| VC1_HI, _LO (0x0C–0x0D), VC2_HI, _LO (0x0E–0x0F), VC3_HI, _LO (0x10–0x11), VC4_HI, _LO (0x12–0x13), VC5_HI, _LO (0x14–0x15) / bq76930, bq76940: VC6_HI, _LO (0x16–0x17), VC7_HI, _LO (0x18–0x19), VC8_HI, _LO (0x1A–0x1B), VC9_HI, _LO (0x1C–0x1D), VC10_HI, _LO (0x1E–0x1F) / bq76940: VC11_HI, _LO (0x20–0x21), VC12_HI, _LO (0x22–0x23), VC13_HI, _LO (0x24–0x25), VC14_HI, _LO (0x26–0x27), VC15_HI, _LO (0x28–0x29) | | | | | | | | |
|--|----|----|-----|-----|-----|-----|----|----|
| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| NAME | — | — | D13 | D12 | D11 | D10 | D9 | D8 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| NAME | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |

D11:8 (Bits 3–0): Cell “x” ADC reading, upper 6 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

D7:0 (Bits 7–0): Cell “x” ADC reading, lower 8 LSB.

Table 7-16. BAT_HI (0x2A) and BAT_LO (0x2B)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-------|-----|-----|-----|-----|-----|-----|----|----|
| NAME | D15 | D14 | D13 | D12 | D11 | D10 | D9 | D8 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| NAME | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |

D15:8 (Bits 7–0): BAT calculation based on adding up Cells 1–15, upper 8 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

D7:0 (Bits 7–0): BAT calculation based on adding up Cells 1–15, lower 8 LSB

Table 7-17. TS1_HI (0x2C) and TS1_LO (0x2D)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-------|----|----|-----|-----|-----|-----|----|----|
| NAME | — | — | D13 | D12 | D11 | D10 | D9 | D8 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| NAME | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |

D11:8 (Bits 3–0): TS1 or DIETEMP ADC reading, upper 6 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

D7:0 (Bits 7–0): TS1 or DIETEMP ADC reading, lower 8 LSB

Table 7-18. TS2_HI (0x2E) and TS2_LO (0x2F)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-------|----|----|-----|-----|-----|-----|----|----|
| NAME | — | — | D13 | D12 | D11 | D10 | D9 | D8 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| NAME | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |

D11:8 (Bits 3–0): TS2 ADC reading, upper 6 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

D7:0 (Bits 7–0): TS2 ADC reading, lower 8 LSB

Table 7-19. TS3_HI (0x30) and TS3_LO (0x31)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-------|----|----|-----|-----|-----|-----|----|----|
| NAME | — | — | D13 | D12 | D11 | D10 | D9 | D8 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| NAME | D7 | D6 | D5 | D4 | D3 | D2 | D1 | D0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |

D11:8 (Bits 3–0): TS3 ADC reading, upper 6 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

D7:0 (Bits 7–0): TS3 ADC reading, lower 8 LSB

Table 7-20. CC_HI (0x32) and CC_LO (0x33)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-------|------|------|------|------|------|------|-----|-----|
| NAME | CC15 | CC14 | CC13 | CC12 | CC11 | CC10 | CC9 | CC8 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| NAME | CC7 | CC6 | CC5 | CC4 | CC3 | CC2 | CC1 | CC0 |
| RESET | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |

CC15:8 (Bits 7–0): Coulomb counter upper 8 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

CC7:0 (Bits 7–0): Coulomb counter lower 8 LSB

Table 7-21. ADCGAIN1 (0x50)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|---|---|---|---|----------|----------|---|---|
| NAME | — | — | — | — | ADCGAIN4 | ADCGAIN3 | — | — |
| RESET | — | — | — | — | — | — | — | — |
| ACCESS | R | R | R | R | R | R | R | R |

Table 7-22. ADCGAIN2 (0x59)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|----------|----------|----------|---|---|---|---|---|
| NAME | ADCGAIN2 | ADCGAIN1 | ADCGAIN0 | — | — | — | — | — |
| RESET | — | — | — | — | — | — | — | — |
| ACCESS | R | R | R | R | R | R | R | R |

ADCGAIN4:3 (Bits 3–2, address 0x50):

ADC GAIN
offset upper 2 MSB

ADCGAIN2:0 (Bits 7–5, address 0x59):

ADC GAIN offset lower 3 LSB

ADCGAIN<4:0> is a production-trimmed value for the ADC transfer function, in units of $\mu\text{V}/\text{LSB}$. The range is $365 \mu\text{V}/\text{LSB}$ to $396 \mu\text{V}/\text{LSB}$, in steps of $1 \mu\text{V}/\text{LSB}$, and may be calculated as follows:

$$\text{GAIN} = 365 \mu\text{V}/\text{LSB} + (\text{ADCGAIN}<4:0>\text{in decimal}) \times (1 \mu\text{V}/\text{LSB})$$

Alternately, a conversion table is provided below:

| ADC GAIN | Gain ($\mu\text{V}/\text{LSB}$) | ADC GAIN | Gain ($\mu\text{V}/\text{LSB}$) |
|----------|-----------------------------------|----------|-----------------------------------|
| 0x00 | 365 | 0x10 | 381 |
| 0x01 | 366 | 0x11 | 382 |
| 0x02 | 367 | 0x12 | 383 |
| 0x03 | 368 | 0x13 | 384 |
| 0x04 | 369 | 0x14 | 385 |
| 0x05 | 370 | 0x15 | 386 |
| 0x06 | 371 | 0x16 | 387 |
| 0x07 | 372 | 0x17 | 388 |
| 0x08 | 373 | 0x18 | 389 |
| 0x09 | 374 | 0x19 | 390 |
| 0x0A | 375 | 0x1A | 391 |
| 0x0B | 376 | 0x1B | 392 |
| 0x0C | 377 | 0x1C | 393 |
| 0x0D | 378 | 0x1D | 394 |
| 0x0E | 379 | 0x1E | 395 |
| 0x0F | 380 | 0x1F | 396 |

Table 7-23. ADCOFFSET (0x51)

| BIT | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|--------|-------------|-------------|-------------|-------------|-------------|-------------|-------------|-------------|
| NAME | ADC OFFSET7 | ADC OFFSET6 | ADC OFFSET5 | ADC OFFSET4 | ADC OFFSET3 | ADC OFFSET2 | ADC OFFSET1 | ADC OFFSET0 |
| RESET | — | — | — | — | — | — | — | — |
| ACCESS | R | R | R | R | R | R | R | R |

ADCOFFSET7:0 (Bits 7–0):

ADC offset, stored in 2's complement format in mV units. Positive full-scale range corresponds to 0x7F and negative full-scale corresponds to 0x80. The full-scale input range is -128 mV to 127 mV , with an LSB of 1 mV .

The table below shows example offsets.

| ADCOFFSET | Offset (mV) |
|-----------|-------------|
| 0x00 | 0 |
| 0x01 | 1 |
| 0x7F | 127 |
| 0x80 | -128 |
| 0x81 | -127 |
| 0xFF | -1 |

8 Application and Implementation

NOTE

Information in the following application section is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The bq769x0 family of battery monitoring AFEs enabling cell parametric measurement and protection is a variety of 3-series to 15-series Li-Ion/Li Polymer battery packs.

To evaluate the performance and configurations of the device users need the bq76940/bq76930/bq76920 Evaluation Software, ([SLUCC539](#)) tool to configure the internal registers for a specific battery pack and application. The Evaluation Software tool is a graphical user-interface tool installed on a PC during development. This can be used in conjunction with the bq76920EVM, bq76930EVM or bq76940EVM.

The bq769x0 devices are expected to be implemented in a system with a microcontroller that can perform additional functions based on the data made collected. The bq78350 is one example of a companion to the bq769x0 family.

8.1.1 Configuring Alternative Cell Counts

Each bq769x0 family of IC's support a variety of cell counts. The following tables provide guidance on which device and which input pins to use, depending on the number of cells in the pack.

Table 8-1. Cell Connections for bq76920

| Cell Input | 3 Cells | 4 Cells | 5 Cells |
|------------|---------|---------|---------|
| VC5–VC4 | CELL 3 | CELL 4 | CELL 5 |
| VC4–VC3 | short | short | CELL 4 |
| VC3–VC2 | short | CELL 3 | CELL 3 |
| VC2–VC1 | CELL 2 | CELL 2 | CELL 2 |
| VC1–VC0 | CELL 1 | CELL 1 | CELL 1 |

Table 8-2. Cell Connections for bq76930

| Cell Input | 6 Cells | 7 Cells | 8 Cells | 9 Cells | 10 Cells |
|------------|---------|---------|---------|---------|----------|
| VC10–VC9 | CELL 6 | CELL 7 | CELL 8 | CELL 9 | CELL 10 |
| VC9–VC8 | short | short | short | short | CELL 9 |
| VC8–VC7 | short | short | CELL 7 | CELL 8 | CELL 8 |
| VC7–VC6 | CELL 5 | CELL 6 | CELL 6 | CELL 7 | CELL 7 |
| VC6–VC5b | CELL 4 | CELL 5 | CELL 5 | CELL 6 | CELL 6 |
| VC5–VC4 | CELL 3 | CELL 4 | CELL 4 | CELL 5 | CELL 5 |
| VC4–VC3 | short | short | short | CELL 4 | CELL 4 |
| VC3–VC2 | short | CELL 3 | CELL 3 | CELL 3 | CELL 3 |
| VC2–VC1 | CELL 2 | CELL 2 | CELL 2 | CELL 2 | CELL 2 |
| VC1–VC0 | CELL 1 | CELL 1 | CELL 1 | CELL 1 | CELL 1 |

Table 8-3. Cell Connections for bq76940

| Cell Input | 9 Cells | 10 Cells | 11 Cells | 12 Cells | 13 Cells | 14 Cells | 15 Cells |
|------------|---------|----------|----------|----------|----------|----------|----------|
| VC15-VC14 | CELL 9 | CELL 10 | CELL 11 | CELL 12 | CELL 13 | CELL 14 | CELL 15 |
| VC14-VC13 | short | short | short | short | short | short | CELL 14 |
| VC13-VC12 | short | short | short | CELL 11 | CELL 12 | CELL 13 | CELL 13 |
| VC12-VC11 | CELL 8 | CELL 9 | CELL 10 | CELL 10 | CELL 11 | CELL 12 | CELL 12 |
| VC11-VC10b | CELL 7 | CELL 8 | CELL 9 | CELL 9 | CELL 10 | CELL 11 | CELL 11 |
| VC10-VC9 | CELL 6 | CELL 7 | CELL 8 | CELL 8 | CELL 9 | CELL 10 | CELL 10 |
| VC9-VC8 | short | short | short | short | short | CELL 9 | CELL 9 |
| VC8-VC7 | short | short | CELL 7 | CELL 7 | CELL 8 | CELL 8 | CELL 8 |
| VC7-VC6 | CELL 5 | CELL 6 | CELL 6 | CELL 6 | CELL 7 | CELL 7 | CELL 7 |
| VC6-VC5b | CELL 4 | CELL 5 | CELL 5 | CELL 5 | CELL 6 | CELL 6 | CELL 6 |
| VC5-VC4 | CELL 3 | CELL 4 | CELL 4 | CELL 4 | CELL 5 | CELL 5 | CELL 5 |
| VC4-VC3 | short | short | short | short | CELL 4 | CELL 4 | CELL 4 |
| VC3-VC2 | short | CELL 3 | CELL 3 | CELL 3 | CELL 3 | CELL 3 | CELL 3 |
| VC2-VC1 | CELL 2 | CELL 2 | CELL 2 | CELL 2 | CELL 2 | CELL 2 | CELL 2 |
| VC1-VC0 | CELL 1 | CELL 1 | CELL 1 | CELL 1 | CELL 1 | CELL 1 | CELL 1 |

8.2 Typical Applications

CAUTION

The external circuitries in the following schematics show minimum requirements to ensure device robustness during cell connection to the PCB and normal operation.

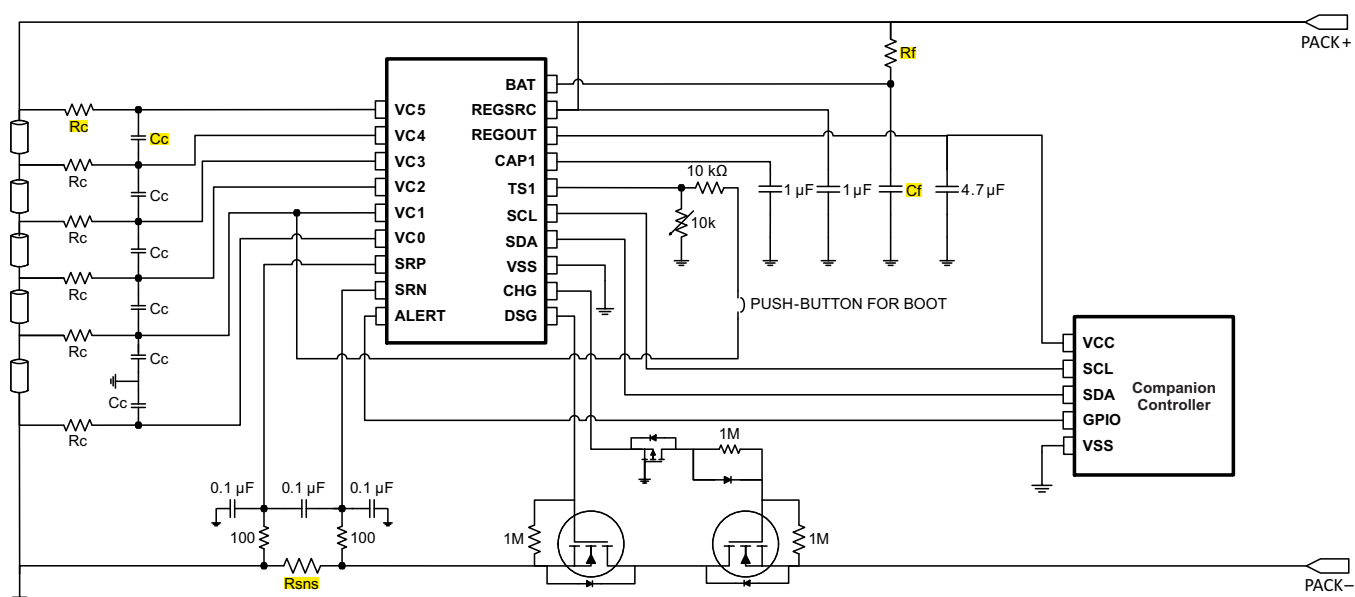


Figure 8-1. bq76920 with bq78350 Companion Controller IC

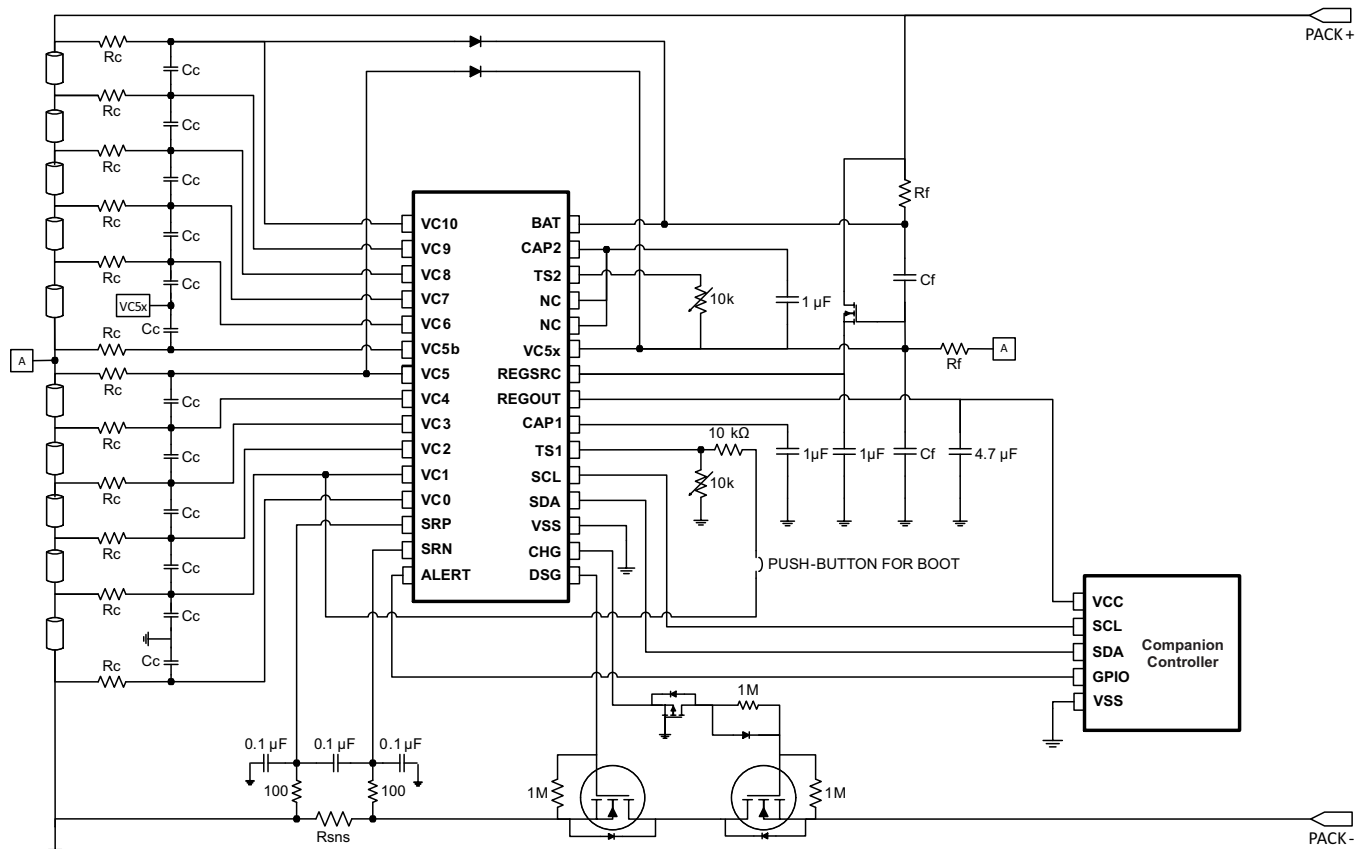
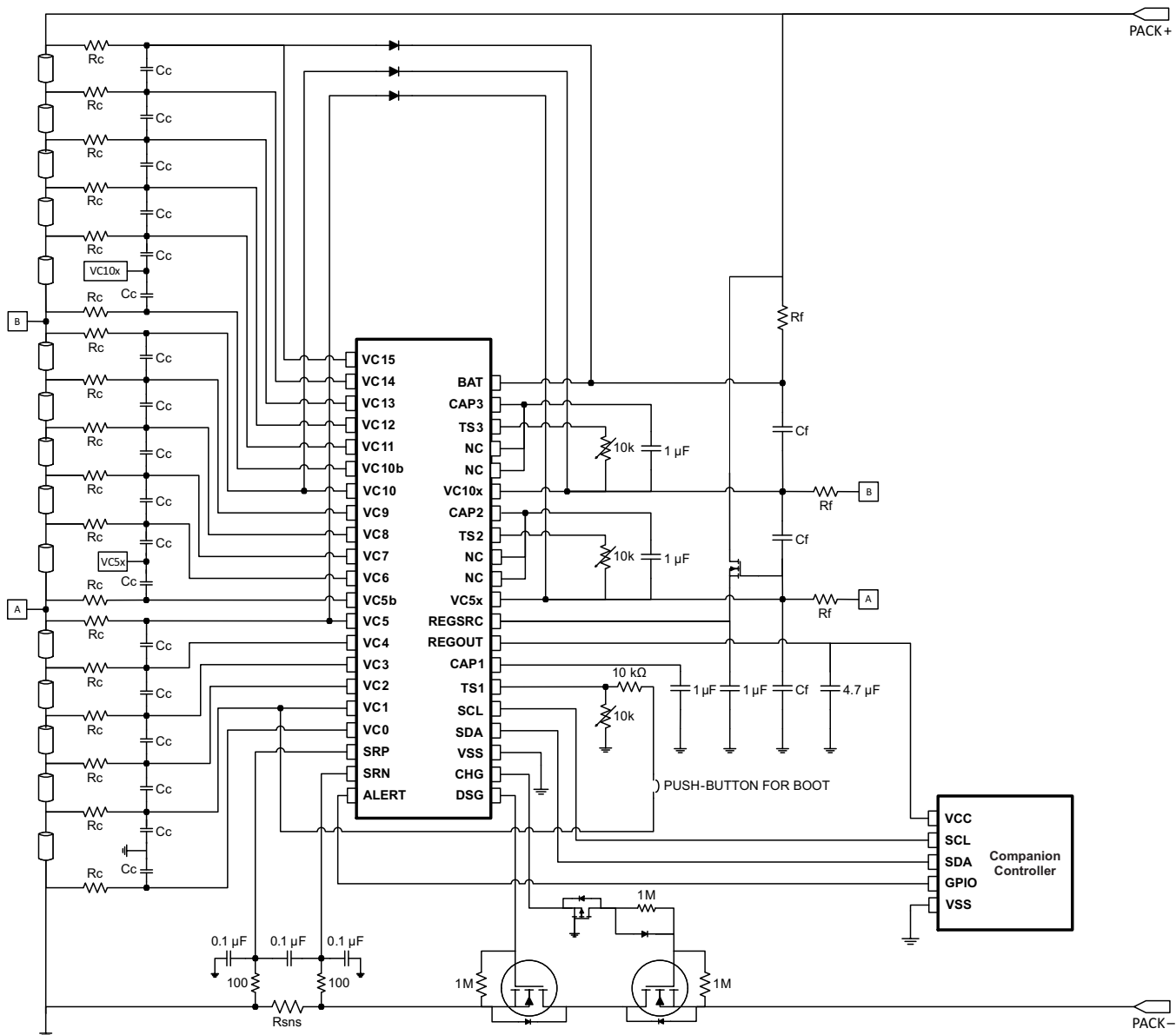


Figure 8-2. bq76930 with bq78350 Companion Controller IC



Copyright © 2016, Texas Instruments Incorporated

Figure 8-3. bq76940 with bq78350 Companion Controller IC

8.2.1 Design Requirements

Table 8-4. bq769x0 Design Requirements

| DESIGN PARAMETER | EXAMPLE VALUE at TA = 25°C |
|----------------------------------|----------------------------|
| Minimum system operating voltage | 24 V |
| Cell minimum operating voltage | 3.0 V |
| Series Cell Count | 8 |
| Charge Voltage | 33.6 V |
| Maximum Charge Current | 3.0 A |
| Peak Discharge Current | 10.0 A |
| OV Protection Threshold | 4.30 V |
| OV Protection Delay | 2s |
| UV Protection Threshold | 2.5 V |

Table 8-4. bq769x0 Design Requirements (continued)

| DESIGN PARAMETER | EXAMPLE VALUE at TA = 25°C |
|------------------------------|----------------------------|
| UV Protection Delay | 4s |
| OCD Protection Threshold Max | 15 A |
| OCD Protection Delay Time | 320 ms |
| SCD Protection Threshold Max | 25 A |
| SCD Protection Delay Time | 100 μ s |

8.2.2 Detailed Design Procedure

To begin the design process, there are some key steps required for component selection and protection configuration.

8.2.2.1 Step-by-Step Design Procedure

- Determine the number of series cells.
 - This value depends on the cell chemistry and the load requirements of the system. For example, to support a minimum battery voltage of 24 V using Li-CO₂ type cells with a cell minimum voltage of 3.0 V, there needs to be at least 8-series cells.
- Select the correct bq769x0 device.
 - For 8-series cells, the bq76930 is needed.
 - For the correct cell connections, see [Table 8-2](#).
- Select the correct protection FETs.
 - The bq76930 uses a low-side drive suitable for N-CH FETs.
 - These FETs should be rated for the maximum:
 - Voltage, which should be approximately 5 V (DC) 10 V (peak) per series cell: for example, 40 V.
 - Current, which should be calculated based on both the maximum DC current and the maximum transient current with some margin: for example, 30 A.
 - Power Dissipation, which can be a factor of the RDS(ON) rating of the FET, the FET package, and the PCB design: for example, 5 W, assuming 5 m Ω RDS(ON).
- **Select the correct sense resistor.**
 - The resistance value should be selected to maximize the input bandwidth use of the coulomb counter range, CC_{RANGE}, but not exceed the absolute maximum ratings.
 - Using the normal max discharge current, RSNS = 200 mV / 10.0 A = 20 m Ω .
 - However, considering I_{SCD} of 25 A and Abs Max SRP–SRN input of –300 mV, RSNS = 300 mV / 25 A = 7.5 m Ω
 - The maximum operating current of the system should also be considered as this should be below the maximum OCD Threshold, which with a RSNS of 7.5 m Ω gives a max OCD current setting of 13.3 A.
 - Further tolerance analysis (value tolerance, temperature variation, and so on) and PCB design margin should also be considered, so RSNS of 5 m Ω would be suitable with a 75-ppm temperature coefficient and power rating of 5 W.
- The bq76930 is chosen, and so the REGSRC pin needs to be powered through a source follower circuit where the FET is used to provide current for REGSRC from the battery positive terminal while reducing the voltage to a suitable value for the IC.
 - The FET also dissipates the power resulting from the load current and dropped voltage external to the IC and care should be taken to ensure the correct dissipation ratings are specified by the chosen FET.

- Configure the Current-based protection settings through PROTECT1 and PROTECT2:
 - Ideal SCD Threshold = $25\text{ A} \times 5\text{ m}\Omega = 125\text{ mV}$.
 - However, the closest options are 111 mV (0x03) and 133 mV (0x04) providing 22.2 A and 26.6 A, respectively. Both options have the RSNS bit = 1.
 - 0x03 (22.2 A) will be used in this example.
 - The SCD delay threshold setting for a 100 μs delay is 0x01.
 - Therefore, PROTECT1 should be programmed with 0x8C.
 - Ideal OCD Threshold = $15\text{ A} \times 5\text{ m}\Omega = 75\text{ mV}$.
 - However, the closest options are 72 mV (0x0A) and 78 mV (0x0B), providing 14.4 A and 15.6 A, respectively. Both options have the RSNS bit = 1.
 - 0x0A (14.4A) will be used in this example.
 - The OCD delay threshold setting for a 320-ms delay is 0x05.
 - Therefore, PROTECT2 should be programmed with 0x5B.

NOTE

Care should be taken when determining the setting of OV_TRIP and UV_TRIP as these are ADC value outputs and correlation to cell voltage also requires consideration of the ADC GAIN and ADC OFFSET registers. More specific details can be found in [Section 7.3.1.2](#).

- Configure the Voltage-based protection settings through OV_TRIP, UV_TRIP and PROTECT3:
 - The selected OV Threshold is 4.30 V.
 - Therefore, OV_TRIP should be programmed with 0xC9.
 - The selected UV Threshold is 2.5 V.
 - Therefore, UV_TRIP should be programmed with 0x1A.
 - The selected OV Delay is 2 s and the selected UV Delay is 4 s.
 - Therefore, PROTECT3 should be programmed with 0x50.

8.2.3 Application Curves

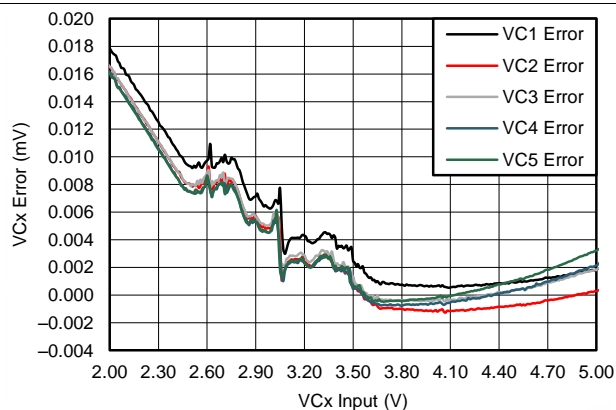


Figure 8-4. bq76930 VCx Error Across Input Range @ 25°C

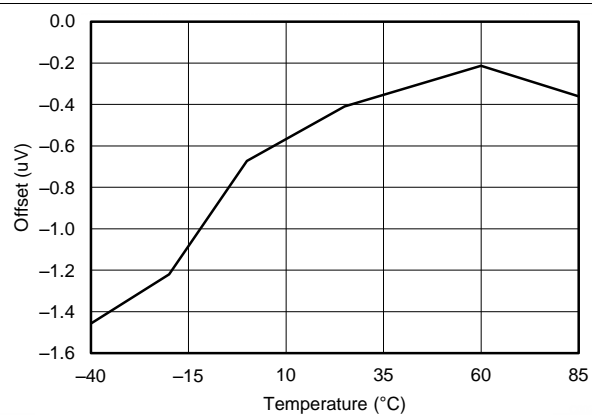


Figure 8-5. Coulomb Counter Offset

9 Power Supply Recommendations

The bq769x0 devices are powered through the BAT and REGSRC pins but the bq76930 and bq76940 have additional 'Power' pins to provide the power to the entire device in the higher cell configurations.

The use of Rf and Cf connected to the BAT pin, noted in the typical application diagrams, are required to filter system transients from disturbing the device power supply. These components should be placed as close as to the IC as possible.

Additionally, for the bq76930 and bq76940 there are additional requirements to ensure a stable power supply to the device. The REGSRC pin is powered through a source follower circuit where the FET is used to provide current for REGSRC from the battery positive terminal while reducing the voltage to a suitable value for the IC. The FET also dissipates the power resulting from the load current and dropped voltage external to the IC and care should be taken to ensure the correct dissipation ratings are specified by the chosen FET.

The bq76920 does not use a FET because the battery voltage is within the REGSRC range.

10 Layout

10.1 Layout Guidelines

It is strongly recommended for best measurement performance to keep high current signals from interfering with the measurement system inputs and ground.

A second key recommendation is to ensure that the bq769x0 input filtering capacitors and power capacitors are connected to a common ground with as little parasitic resistance between the connections as possible.

10.2 Layout Example

Figure 10-1 shows a guideline of how to place key components compared to respective ground zones, based on the bq76920/30/40 EVMs.

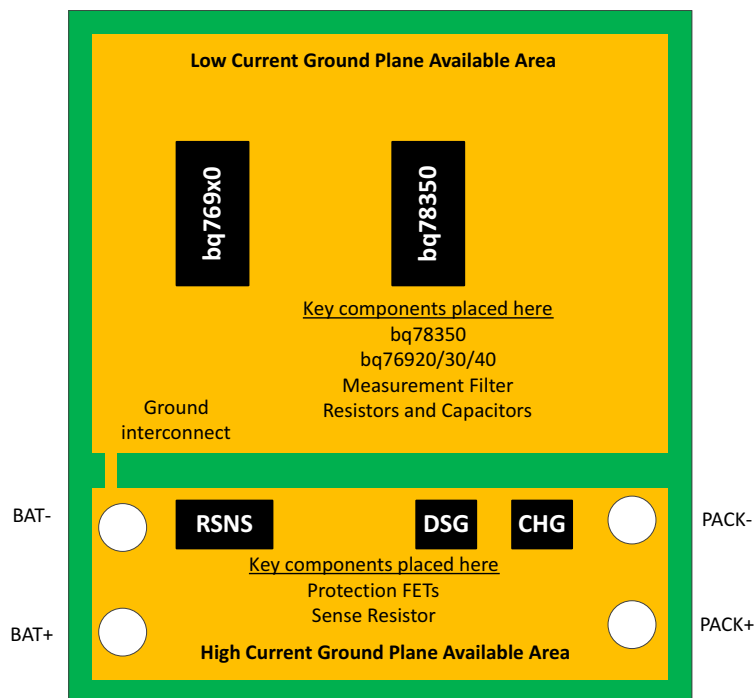


Figure 10-1. System Component Placement Layout vs. Ground Zone Guide

CAUTION

Care should be taken when placing key power pin capacitors to minimize PCB trace impedances. These impedances could result in device resets or other unexpected operations when the device is at peak power consumption.

Although not shown in the diagrams, this caution also applies to the resistor and capacitor network surrounding the current sense resistor.

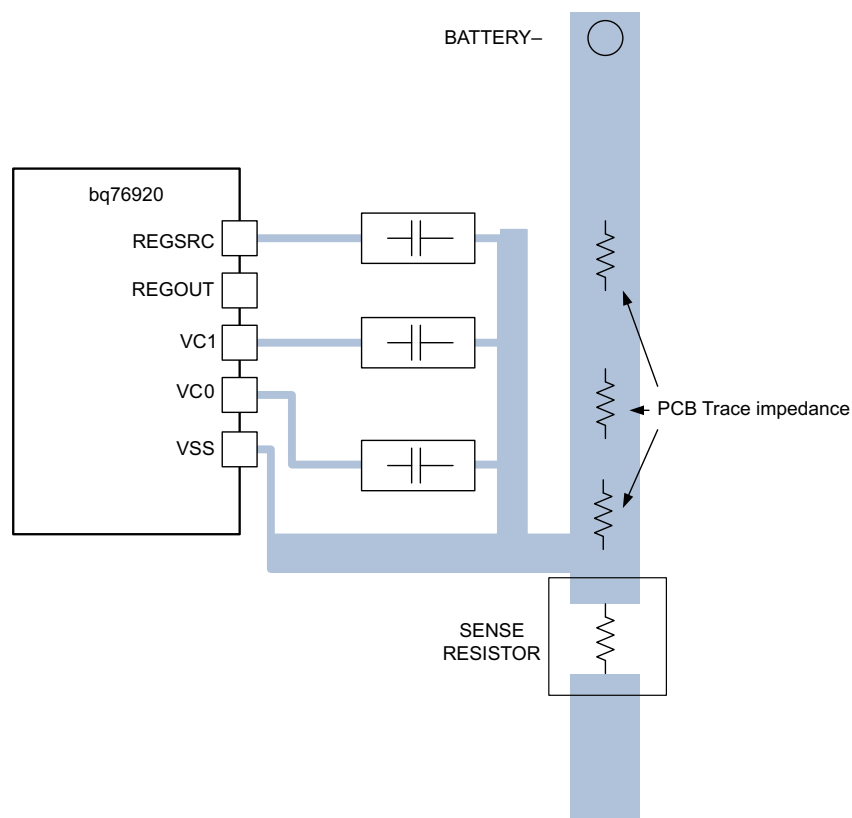


Figure 10-2.
Good Layout: Input Capacitor Grounding with Low Parasitic PCB Impedance

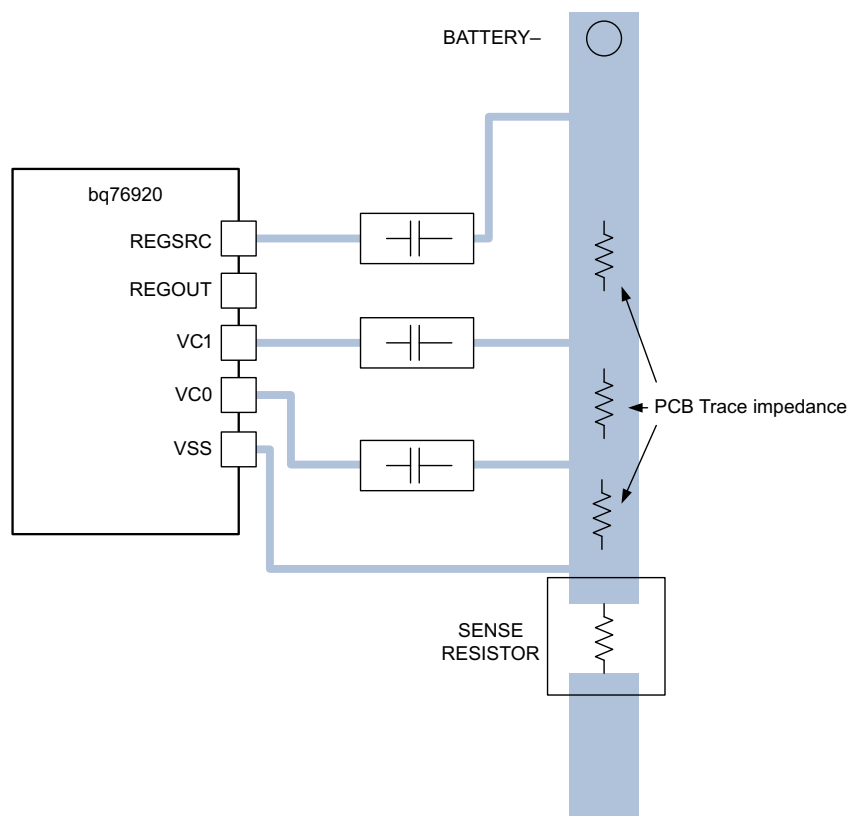


Figure 10-3.
Weak Layout: Input Capacitor Grounding with High Parasitic PCB Impedance

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation, see the following: *bq76920 Evaluation Module User's Guide* ([SLVU924](#)), and *bq76920, bq76930, bq76940 AFE FAQ* ([SLUUB41](#)).

11.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 11-1. Related Links

| PARTS | PRODUCT FOLDER | SAMPLE & BUY | TECHNICAL DOCUMENTS | TOOLS & SOFTWARE | SUPPORT & COMMUNITY |
|---------|----------------------------|----------------------------|----------------------------|----------------------------|----------------------------|
| bq76920 | Click here | Click here | Click here | Click here | Click here |
| bq76930 | Click here | Click here | Click here | Click here | Click here |
| bq76940 | Click here | Click here | Click here | Click here | Click here |

11.2.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](#), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

TI Embedded Processors Wiki *Texas Instruments Embedded Processors Wiki*. Established to help developers get started with Embedded Processors from Texas Instruments and to foster innovation and growth of general knowledge about the hardware and software surrounding these devices.

11.3 Trademarks

E2E is a trademark of Texas Instruments.

I²C is a trademark of NXP B.V. Corporation.

All other trademarks are the property of their respective owners.

11.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead/Ball Finish (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|---------------|--------------|--------------------|------|----------------|----------------------------|-------------------------|----------------------|--------------|-------------------------|-------------------------|
| BQ7692000PW | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7692000 | Samples |
| BQ7692000PWR | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7692000 | Samples |
| BQ7692003PW | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7692003 | Samples |
| BQ7692003PWR | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7692003 | Samples |
| BQ7692006PW | ACTIVE | TSSOP | PW | 20 | 70 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7692006 | Samples |
| BQ7692006PWR | ACTIVE | TSSOP | PW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7692006 | Samples |
| BQ7693000DBT | ACTIVE | TSSOP | DBT | 30 | 60 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693000 | Samples |
| BQ7693000DBTR | ACTIVE | TSSOP | DBT | 30 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693000 | Samples |
| BQ7693001DBT | ACTIVE | TSSOP | DBT | 30 | 60 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693001 | Samples |
| BQ7693001DBTR | ACTIVE | TSSOP | DBT | 30 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693001 | Samples |
| BQ7693002DBT | ACTIVE | TSSOP | DBT | 30 | 60 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693002 | Samples |
| BQ7693002DBTR | ACTIVE | TSSOP | DBT | 30 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693002 | Samples |
| BQ7693003DBT | ACTIVE | TSSOP | DBT | 30 | 60 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693003 | Samples |
| BQ7693003DBTR | ACTIVE | TSSOP | DBT | 30 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693003 | Samples |
| BQ7693006DBT | ACTIVE | TSSOP | DBT | 30 | 60 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693006 | Samples |
| BQ7693006DBTR | ACTIVE | TSSOP | DBT | 30 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693006 | Samples |
| BQ7693007DBT | ACTIVE | TSSOP | DBT | 30 | 60 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693007 | Samples |

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead/Ball Finish (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|---------------|--------------|--------------------|------|----------------|----------------------------|-------------------------|----------------------|--------------|-------------------------|-------------------------|
| BQ7693007DBTR | ACTIVE | TSSOP | DBT | 30 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7693007 | Samples |
| BQ7694000DBT | ACTIVE | TSSOP | DBT | 44 | 40 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694000 | Samples |
| BQ7694000DBTR | ACTIVE | TSSOP | DBT | 44 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694000 | Samples |
| BQ7694001DBT | ACTIVE | TSSOP | DBT | 44 | 40 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694001 | Samples |
| BQ7694001DBTR | ACTIVE | TSSOP | DBT | 44 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694001 | Samples |
| BQ7694002DBT | ACTIVE | TSSOP | DBT | 44 | 40 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694002 | Samples |
| BQ7694002DBTR | ACTIVE | TSSOP | DBT | 44 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694002 | Samples |
| BQ7694003DBT | ACTIVE | TSSOP | DBT | 44 | 40 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694003 | Samples |
| BQ7694003DBTR | ACTIVE | TSSOP | DBT | 44 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694003 | Samples |
| BQ7694006DBT | ACTIVE | TSSOP | DBT | 44 | 40 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694006 | Samples |
| BQ7694006DBTR | ACTIVE | TSSOP | DBT | 44 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | BQ7694006 | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| BQ7692000PWR | TSSOP | PW | 20 | 2000 | 330.0 | 16.4 | 6.95 | 7.1 | 1.6 | 8.0 | 16.0 | Q1 |
| BQ7692003PWR | TSSOP | PW | 20 | 2000 | 330.0 | 16.4 | 6.95 | 7.1 | 1.6 | 8.0 | 16.0 | Q1 |
| BQ7692006PWR | TSSOP | PW | 20 | 2000 | 330.0 | 16.4 | 6.95 | 7.1 | 1.6 | 8.0 | 16.0 | Q1 |

TAPE AND REEL BOX DIMENSIONS

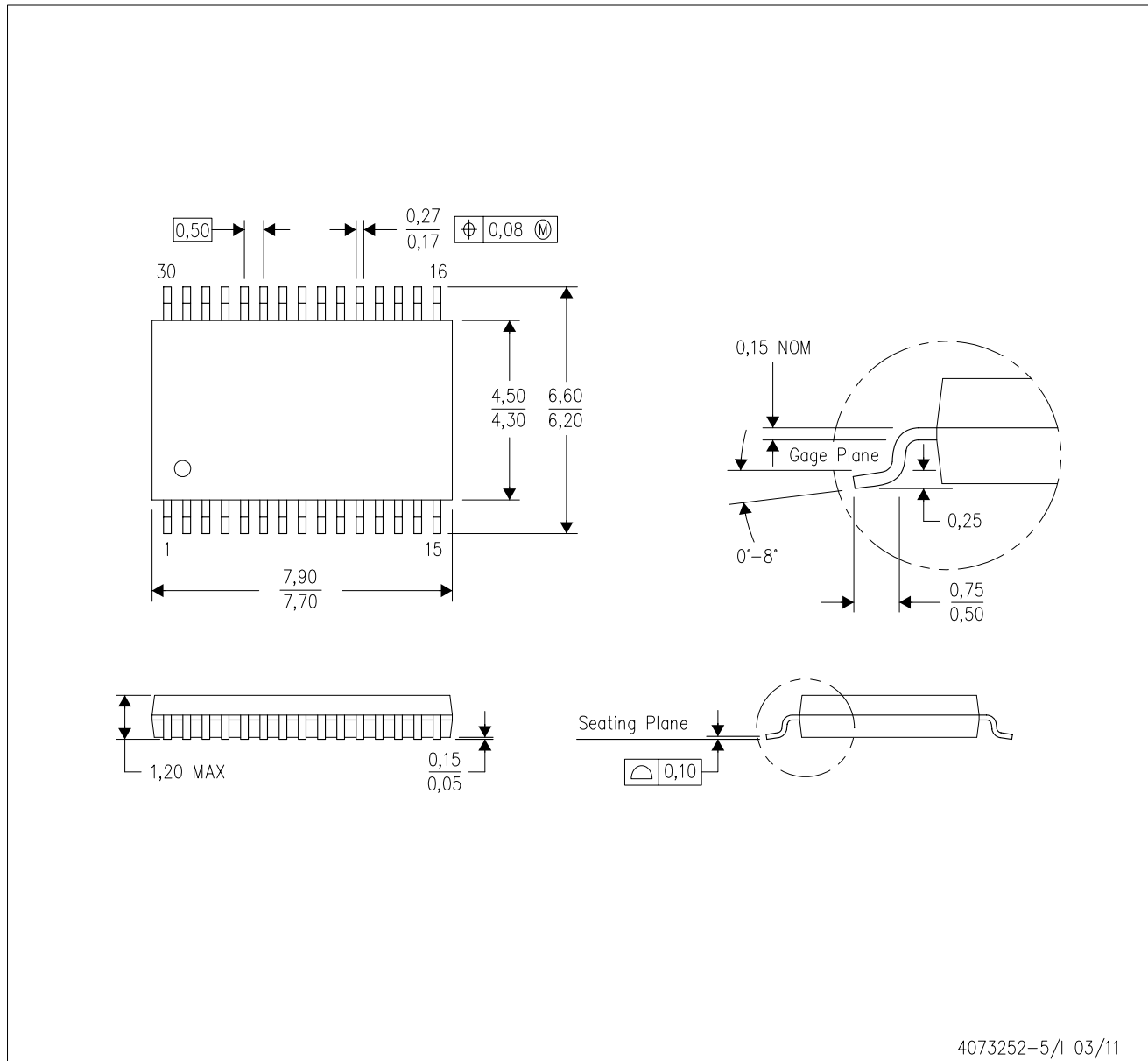


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|--------------|--------------|-----------------|------|------|-------------|------------|-------------|
| BQ7692000PWR | TSSOP | PW | 20 | 2000 | 367.0 | 367.0 | 38.0 |
| BQ7692003PWR | TSSOP | PW | 20 | 2000 | 367.0 | 367.0 | 38.0 |
| BQ7692006PWR | TSSOP | PW | 20 | 2000 | 367.0 | 367.0 | 38.0 |

DBT (R-PDSO-G30)

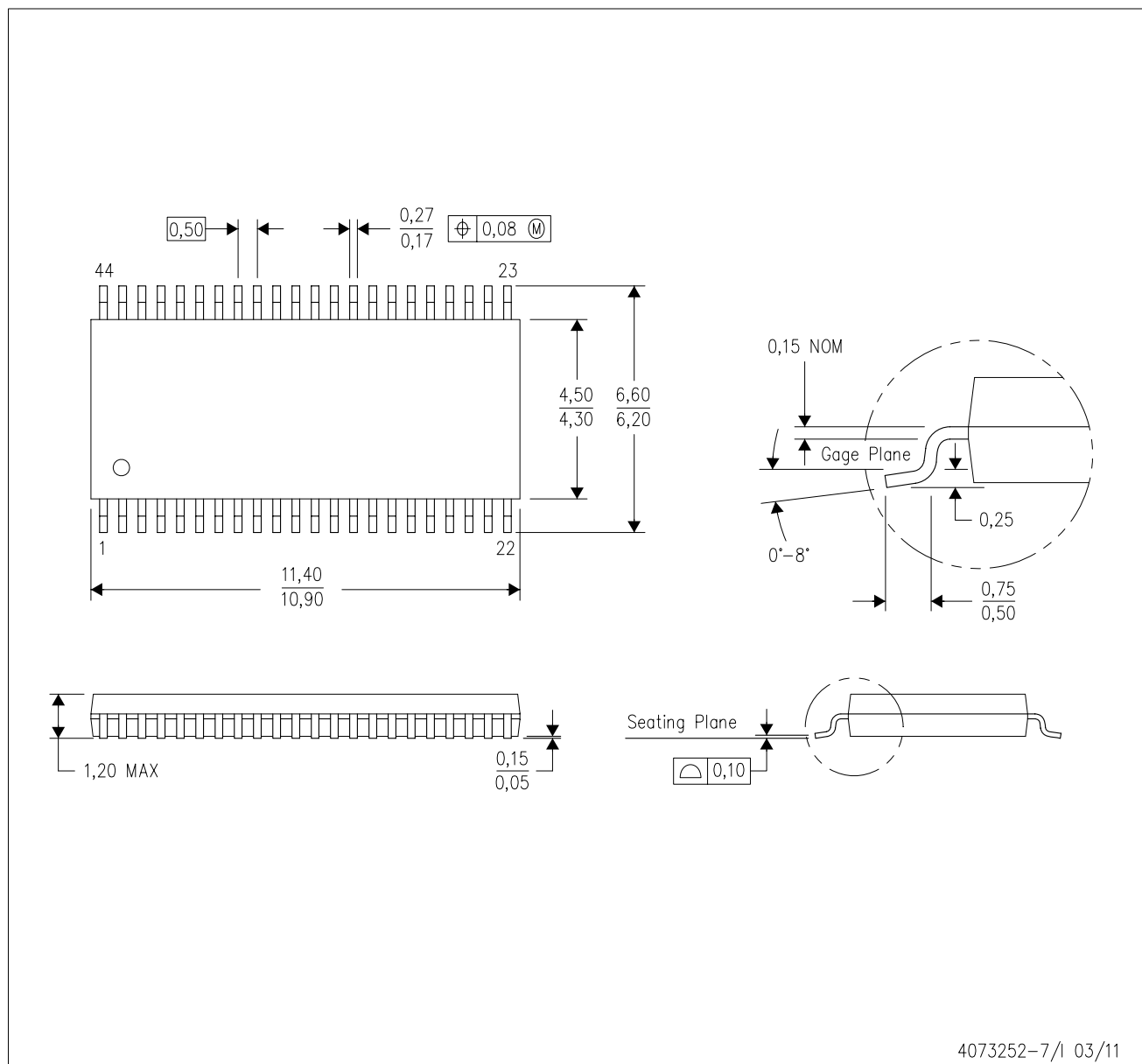
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion.
 - D. Falls within JEDEC MO-153.

DBT (R-PDSO-G44)

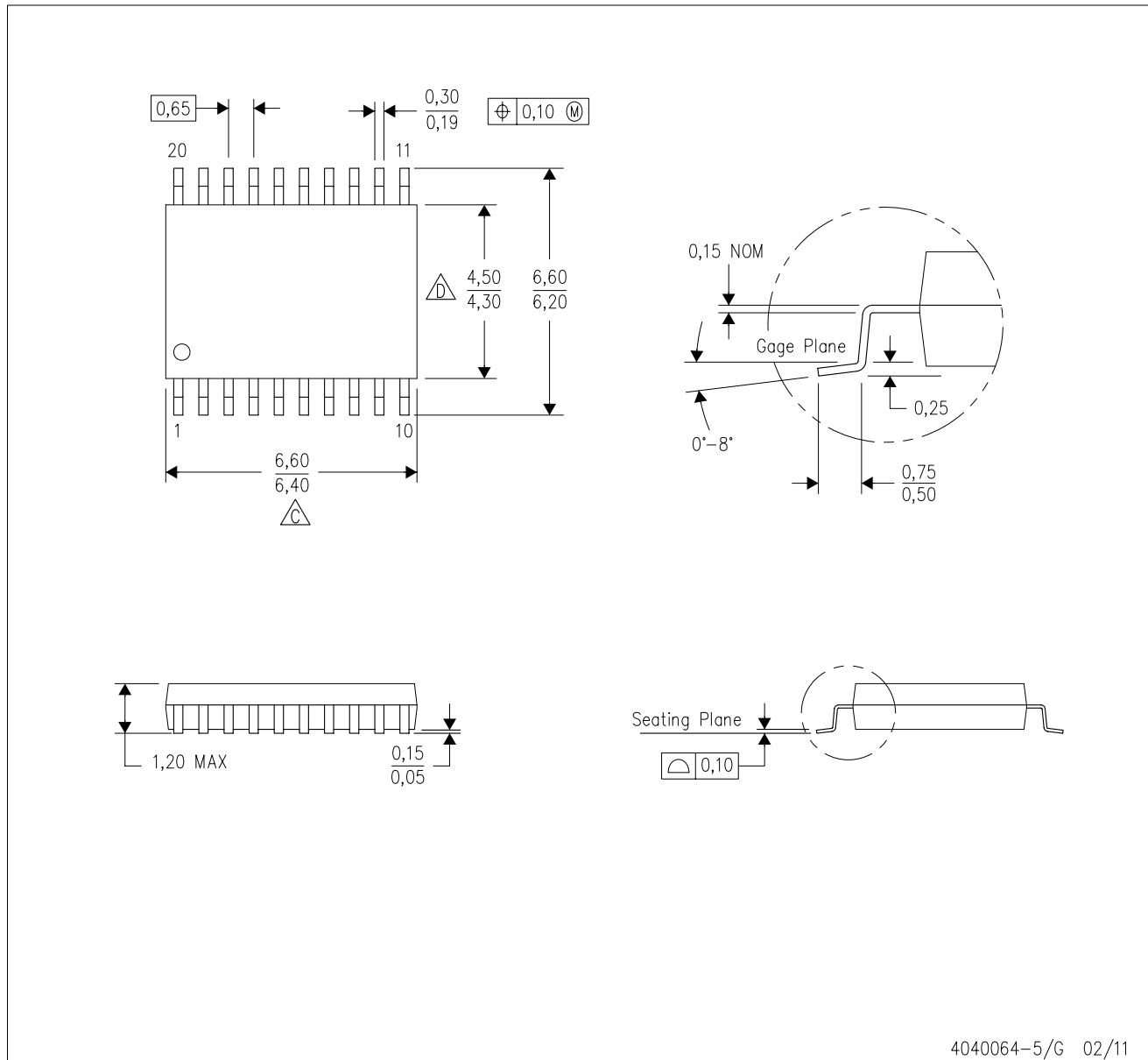
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion.

PW (R-PDSO-G20)

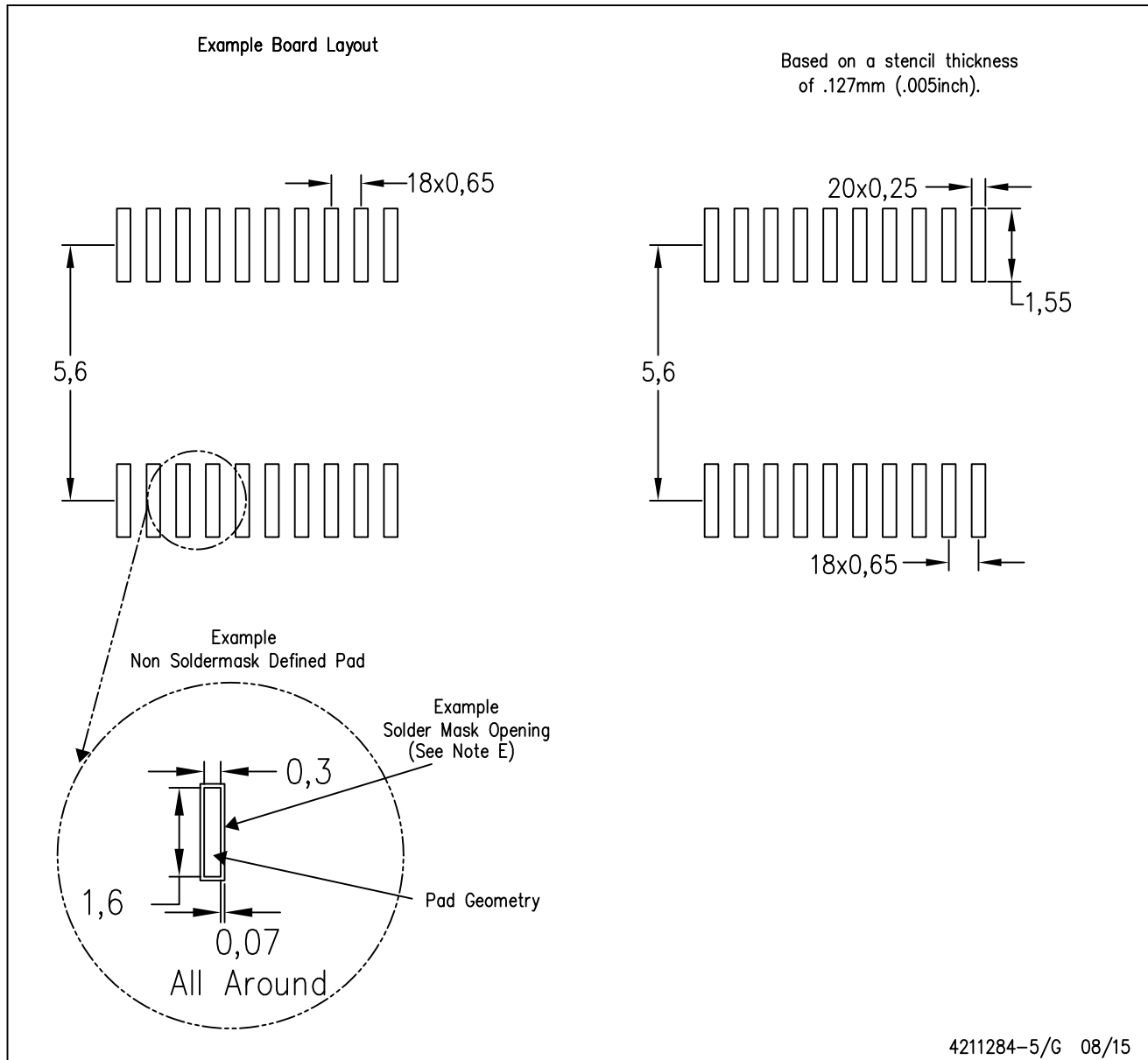
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
 - E. Falls within JEDEC MO-153

PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate design.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products

| | |
|------------------------------|--|
| Audio | www.ti.com/audio |
| Amplifiers | amplifier.ti.com |
| Data Converters | dataconverter.ti.com |
| DLP® Products | www.dlp.com |
| DSP | dsp.ti.com |
| Clocks and Timers | www.ti.com/clocks |
| Interface | interface.ti.com |
| Logic | logic.ti.com |
| Power Mgmt | power.ti.com |
| Microcontrollers | microcontroller.ti.com |
| RFID | www.ti-rfid.com |
| OMAP Applications Processors | www.ti.com/omap |
| Wireless Connectivity | www.ti.com/wirelessconnectivity |

Applications

| | |
|-------------------------------|--|
| Automotive and Transportation | www.ti.com/automotive |
| Communications and Telecom | www.ti.com/communications |
| Computers and Peripherals | www.ti.com/computers |
| Consumer Electronics | www.ti.com/consumer-apps |
| Energy and Lighting | www.ti.com/energy |
| Industrial | www.ti.com/industrial |
| Medical | www.ti.com/medical |
| Security | www.ti.com/security |
| Space, Avionics and Defense | www.ti.com/space-avionics-defense |
| Video and Imaging | www.ti.com/video |

TI E2E Community

e2e.ti.com